

YITP Workshop on Quantum
Information Physics
August 7th 2013

~ Implementation of quantum energy teleportation via the Quantum Hall System ~

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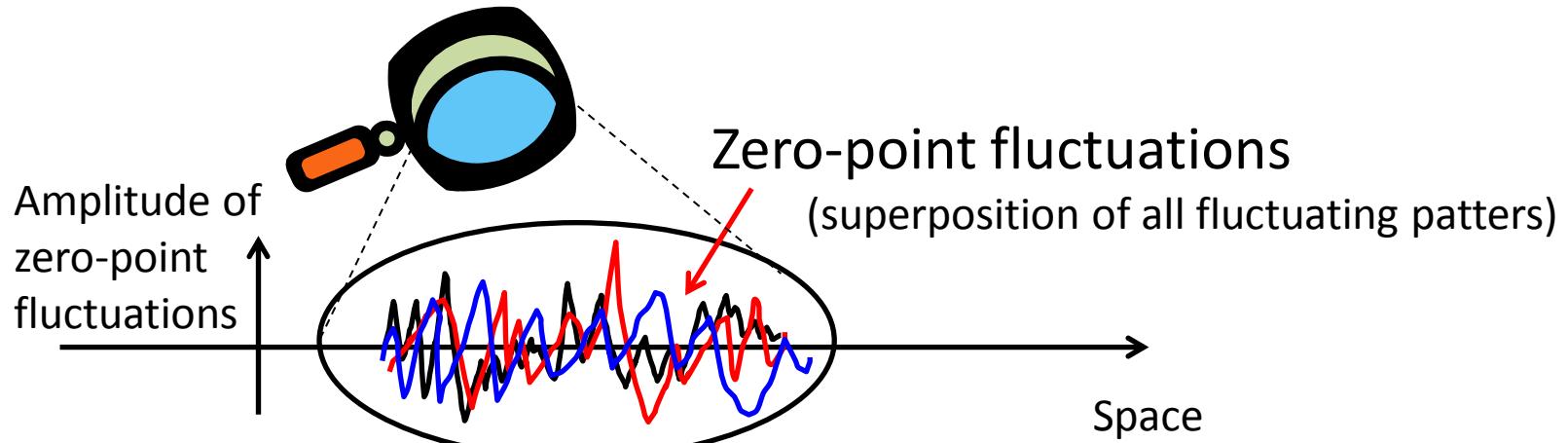
Takeshi Noda
Takaaki Noma



Material science
(provides high quality
semiconductor wafer)

Can zero-point energy be extracted from a vacuum state?

Many-body system in the vacuum state/ground state

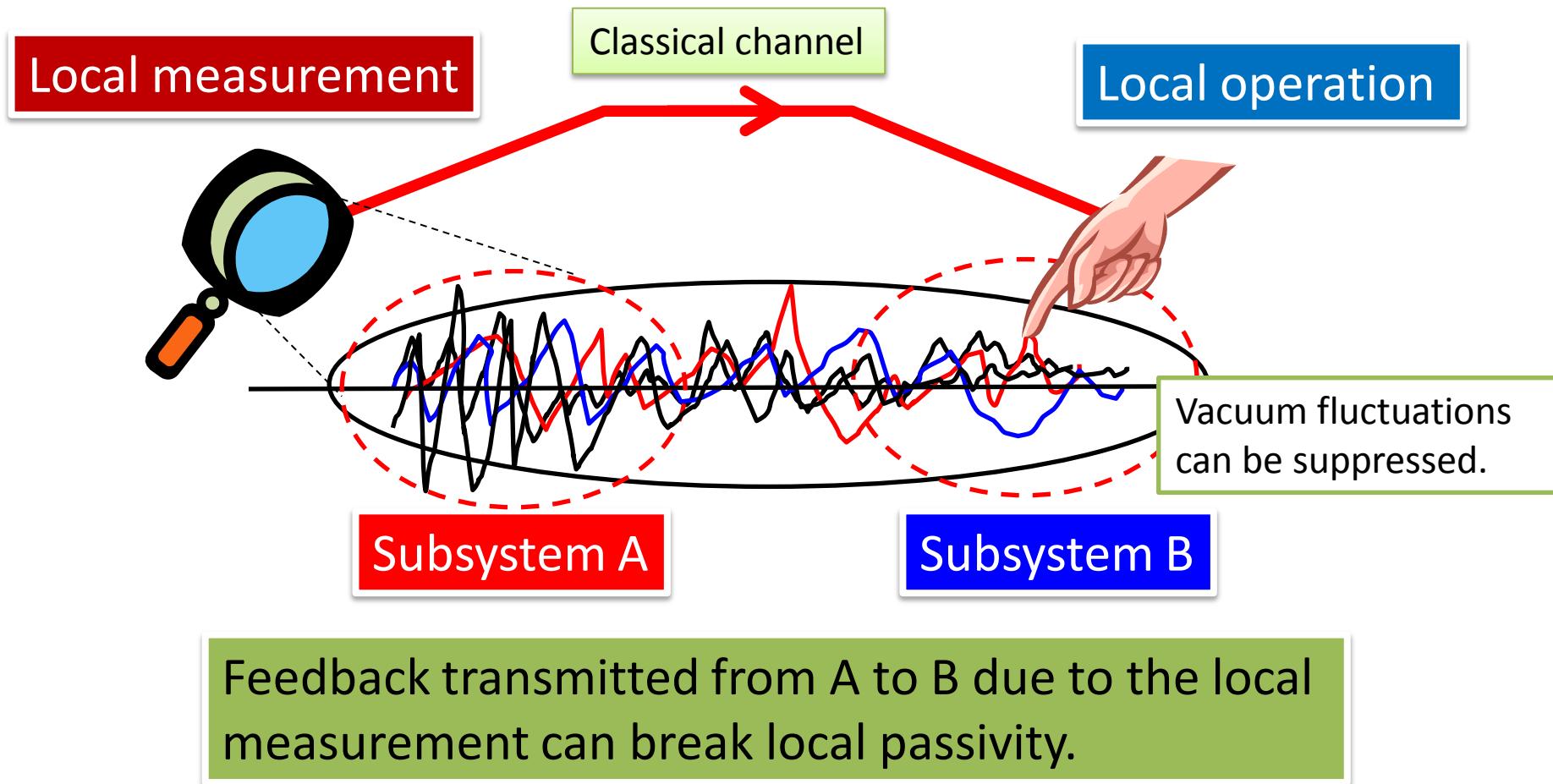


A many-body system in the vacuum state possesses a zero-point energy, however, it is not possible to extract the zero-point energy from the vacuum state by any operations (as it would require a state to exist with lower energy than vacuum).

Measurement (operation) always injects energy into the vacuum.
~ The passivity of a vacuum state ~

Passivity of a *local* vacuum state can be broken

M. Hotta, Phys. Lett. A 372, 5671 (2008), Phys. Rev. D 78, 045006 (2008)



From the “Energy” viewpoint

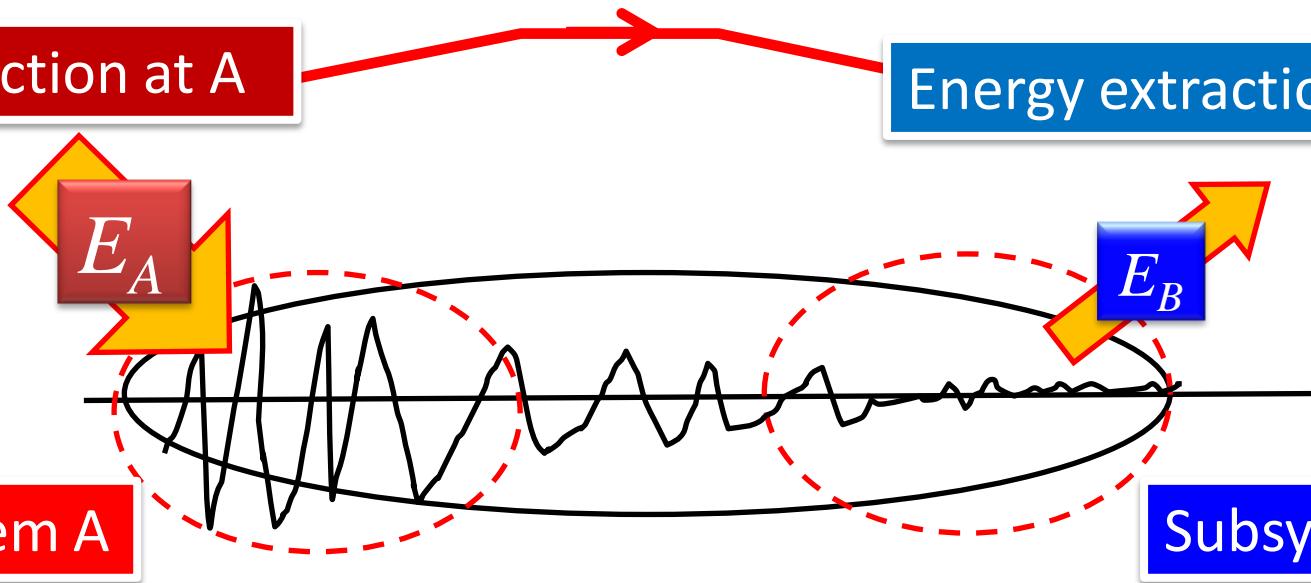
Measurement result

Energy injection at A

Energy extraction at B

Subsystem A

Subsystem B



No entity to transport energy



“Quantum energy teleportation (QET)”

M. Hotta, Phys. Lett. A 372, 5671 (2008), Phys. Rev. D 78, 045006 (2008)

The total energy of the system is positive because $E_B < E_A$

Status of QET study

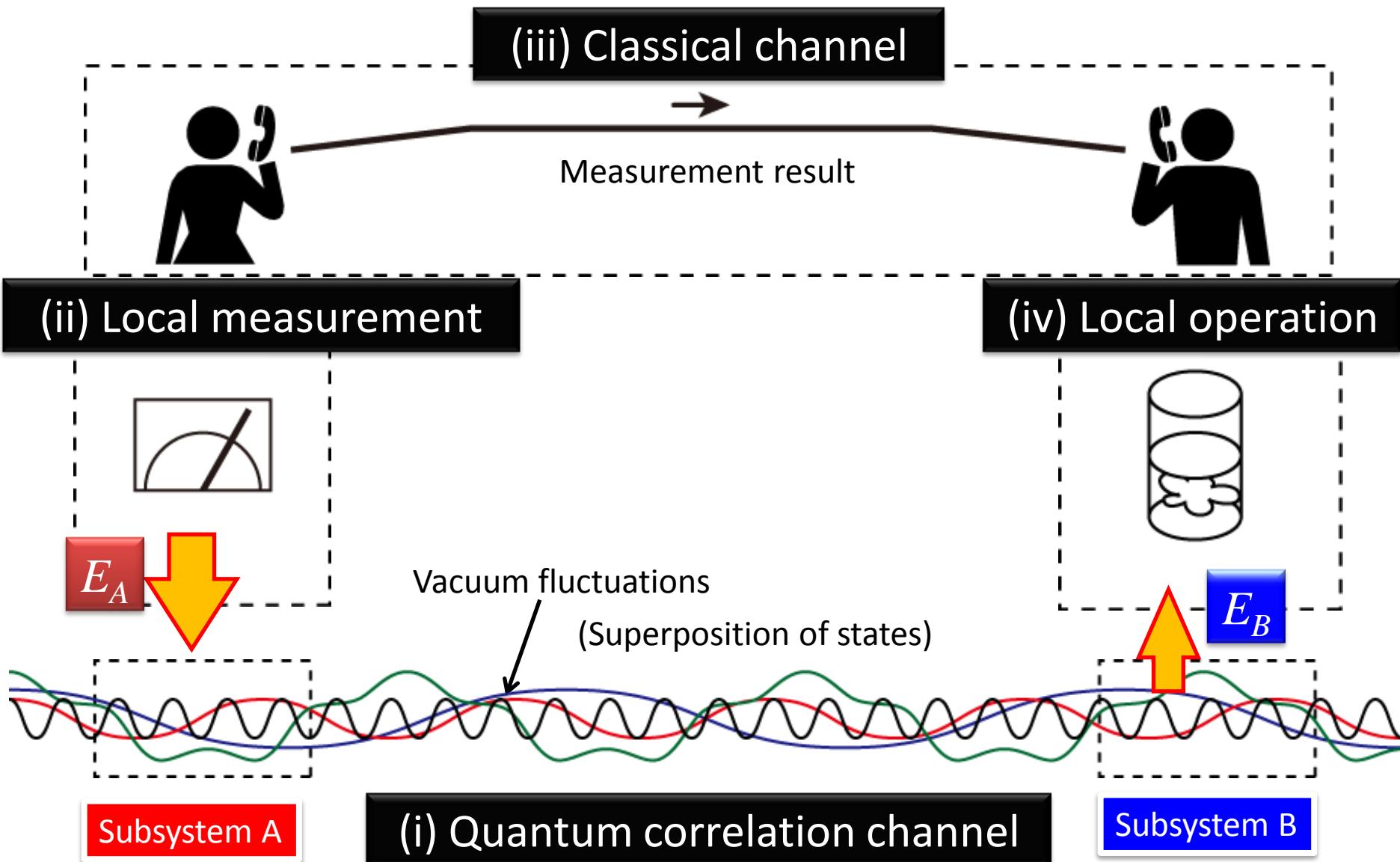
The validity of this protocol has been confirmed *mathematically*, but its *physical significance* remains unclear.

- What type of **physical system** is necessary for implementing this protocol?
- What is the composition of the quantum correlation channel?
- Can significant amounts of energy be “teleported” to a significant remote place?

In this talk.....

- Discuss a more realistic possible implementation and theoretically estimate the order of “teleported” energy using reasonable experimental parameters.
- Report recent experimental progress.

Four key ingredients for QET



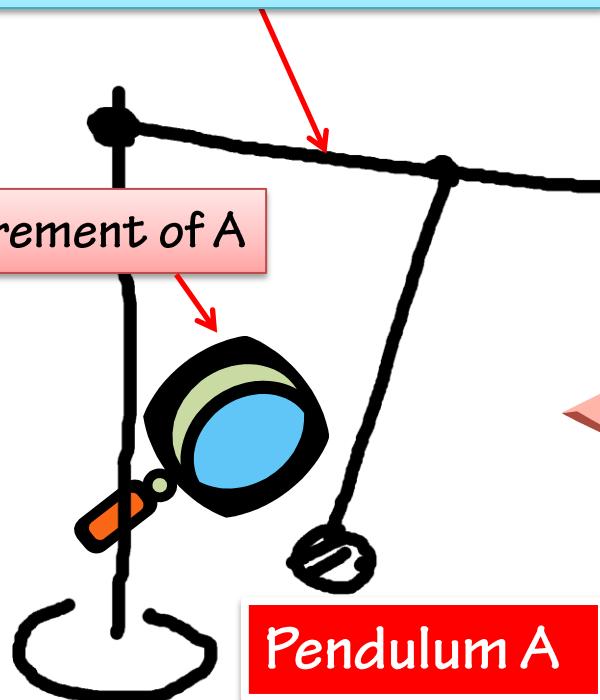
Classical analogue to QET

~ coupled pendulums ~

Can you reduce the amplitude of the oscillations of Pendulum B and gain energy from it without seeing it?

Wire = quantum correlation channel
 (= vacuum state entanglement)

Local measurement of A

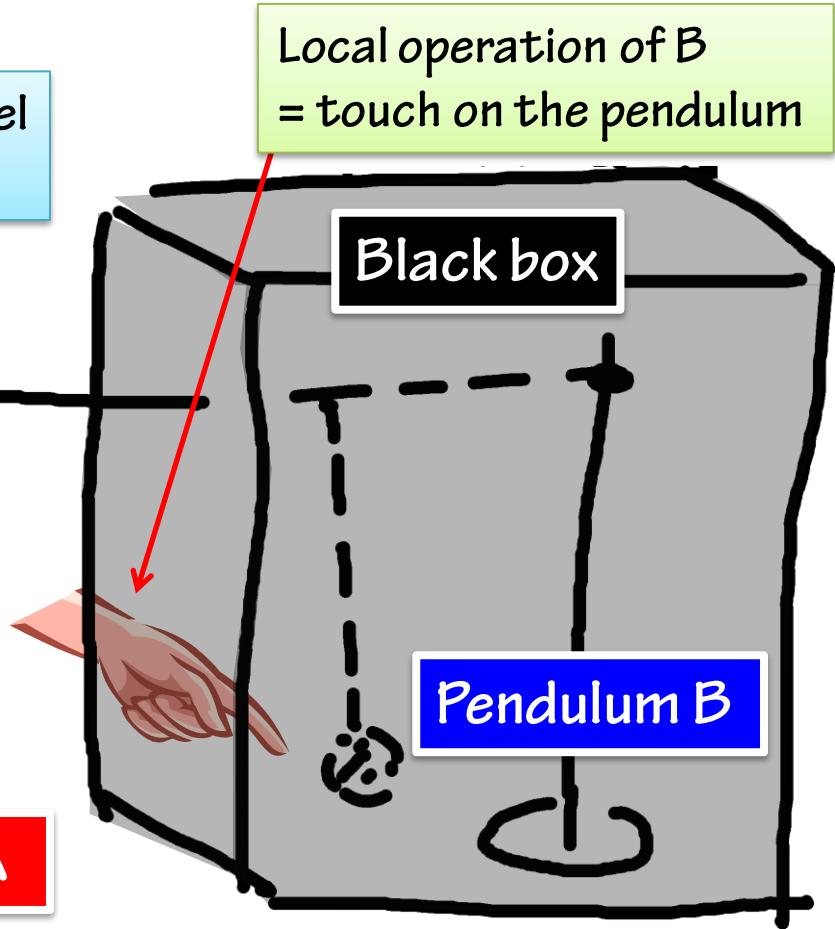


Pendulum A

Local operation of B
= touch on the pendulum

Black box

Pendulum B



Oscillations of pendulums = zero-point fluctuations

Requirements to verify the quantum energy teleportation (QET)

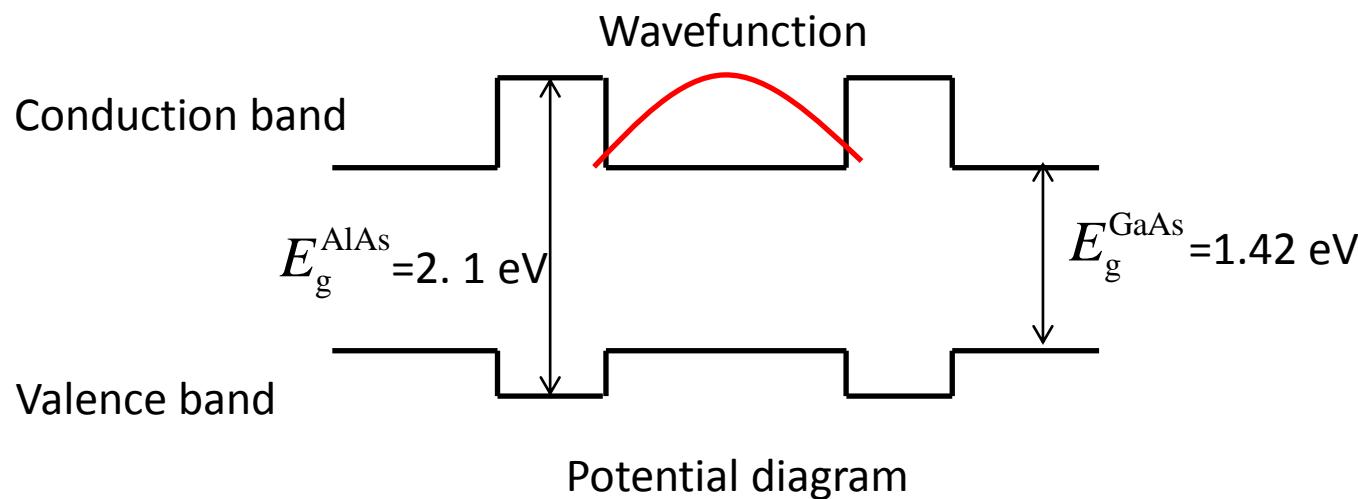
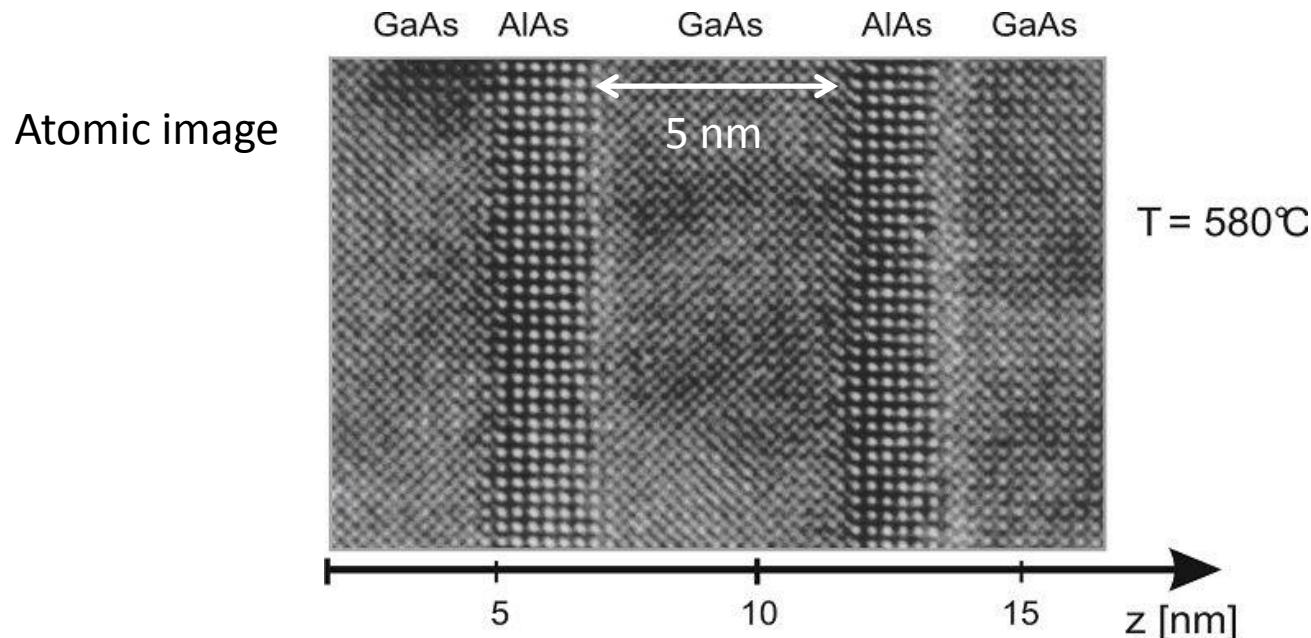
- (1) Dissipationless system
- (2) Quantum correlation channel with macroscopic correlation length
- (3) Detection and operation schemes for well-defined fluctuations in the vacuum state
- (4) Suitable implementation of local operations and classical communication (LOCC)

A quantum Hall system meets all these criteria.

What is a quantum Hall system?

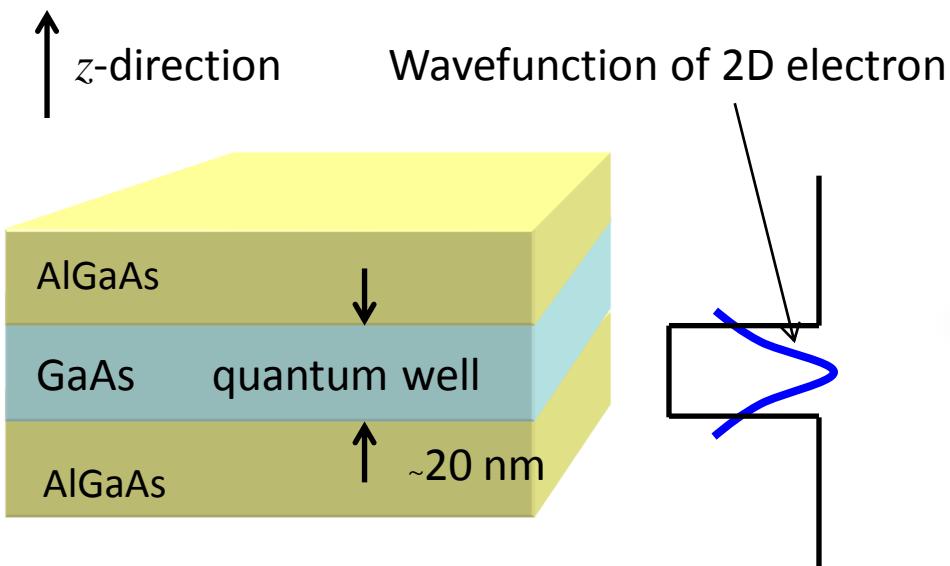
Two-dimensional electron system
in a strong magnetic field.

Cross-sectional view of 5-nm semiconductor quantum well obtained by electron microscopy

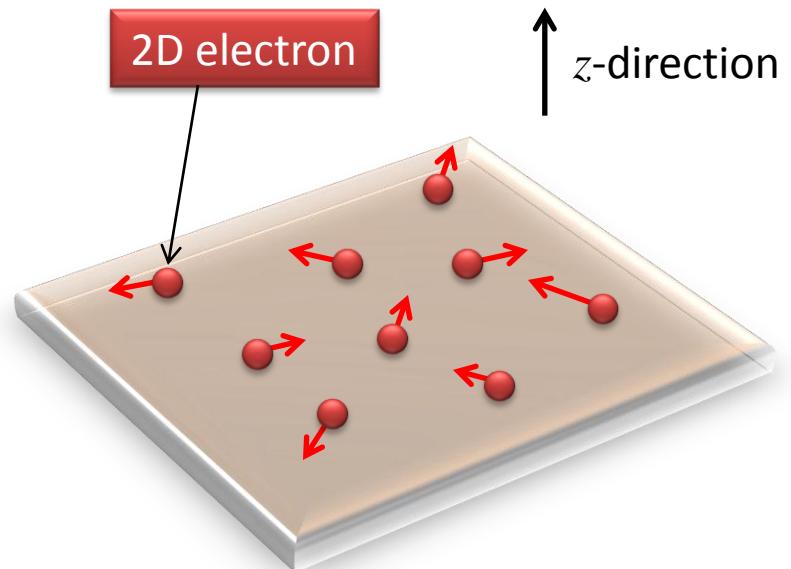


What is a quantum Hall system?

Two-dimensional electron system



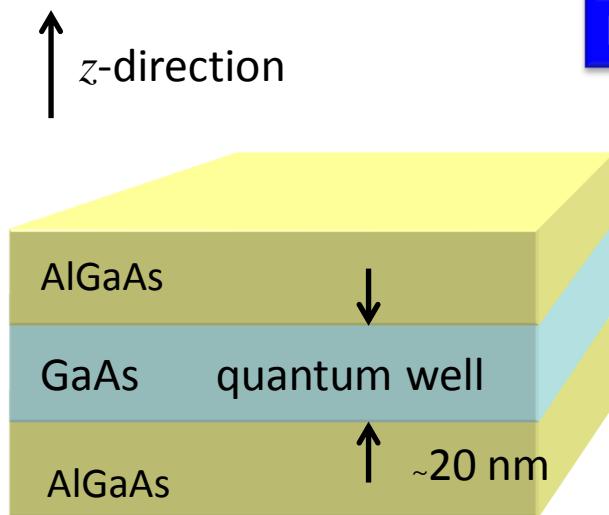
Electrons are confined in
the quantum well



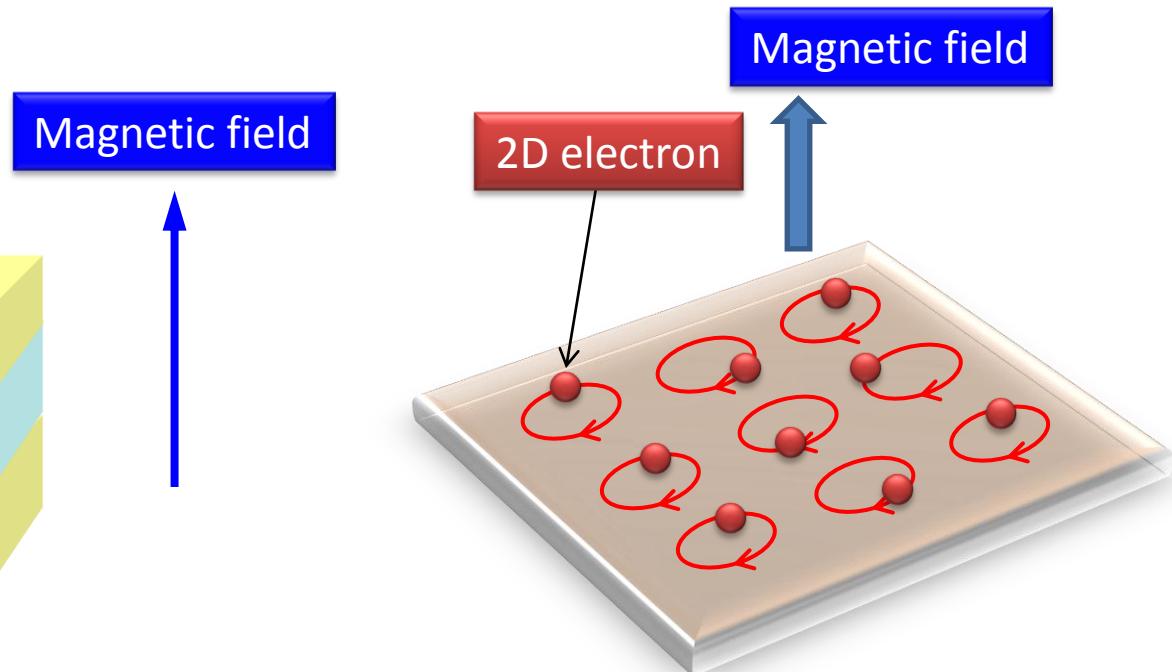
Momentum of the z -direction is quantized
(Electrons move freely in the xy -plane)

What is a quantum Hall system?

2D electrons in a magnetic field



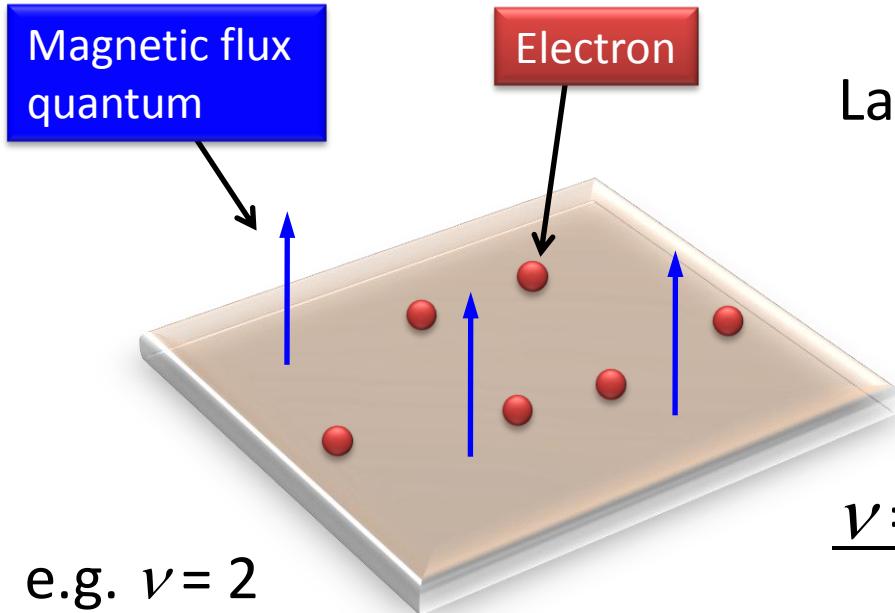
Electrons are confined in
the quantum well



Landau quantization
Cyclotron motion

$$H_0 = \frac{1}{2m^*} (\mathbf{p} + e\mathbf{A})^2$$
$$\nabla \times \mathbf{A} = \mathbf{B}$$

Landau level filling factor ν



e.g. $\nu = 2$

Landau level filling factor

$$\nu = \frac{n_e}{n_\phi} \leftarrow \begin{array}{l} \text{Density of Electrons} \\ \text{Density of flux quanta} \end{array}$$

$\nu = \text{integer:}$

Integer quantum Hall effect

~ Landau quantization of electrons

$\nu = \text{rational fraction:}$

Fractional quantum Hall effect

~ Strong Coulomb interaction

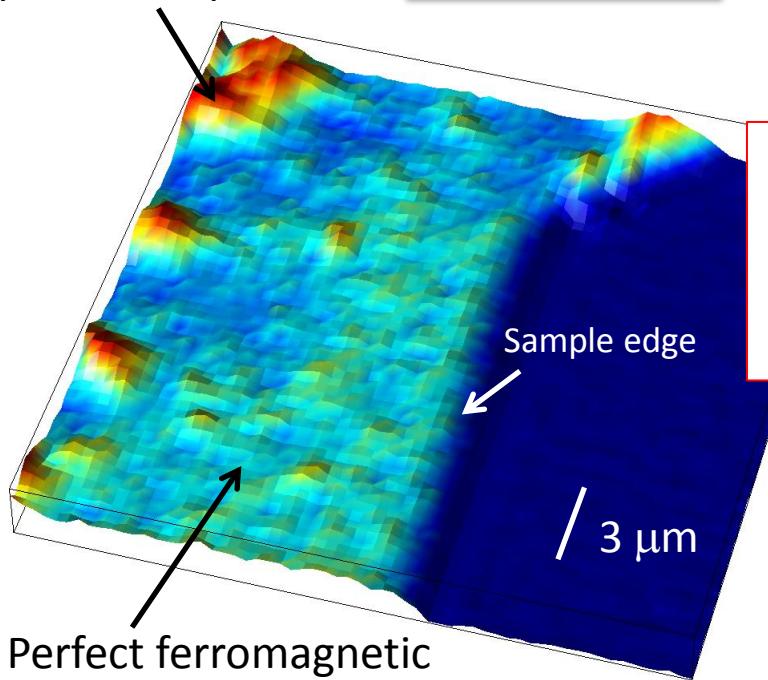
~ Incompressible quantum liquid

Real-space imaging of fractional quantum Hall states

(Image of electron spin polarization)

Nonmagnetic
quantum liquid

$\nu = 0.6659$

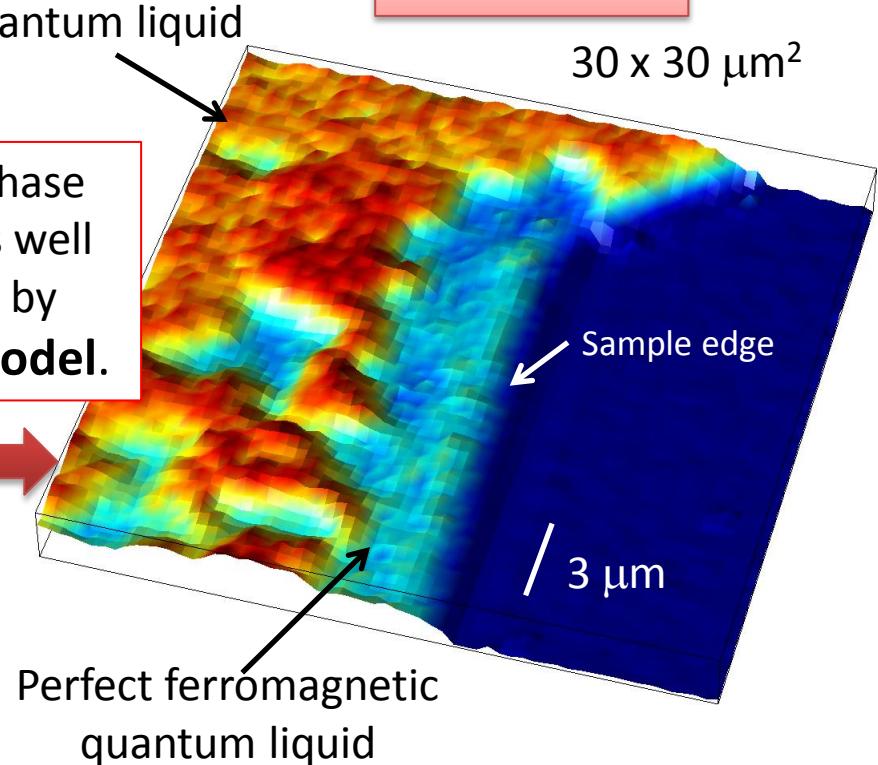


Nonmagnetic
quantum liquid

$\nu = 0.6678$

30 x 30 μm^2

1st order phase transition is well described by
2D Ising model.



Conditions

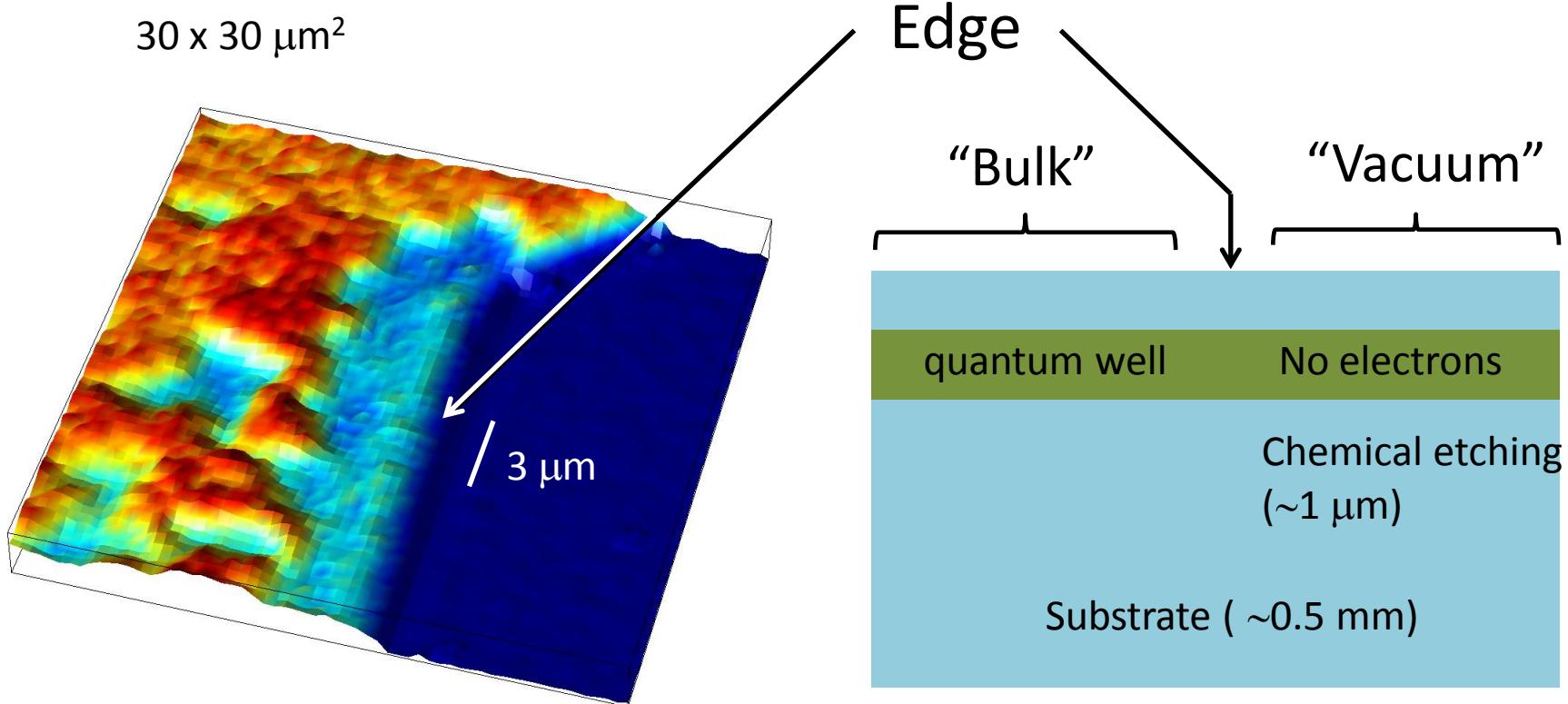
Filling factor : $\nu \sim 2/3$

Temperature: 70 mK

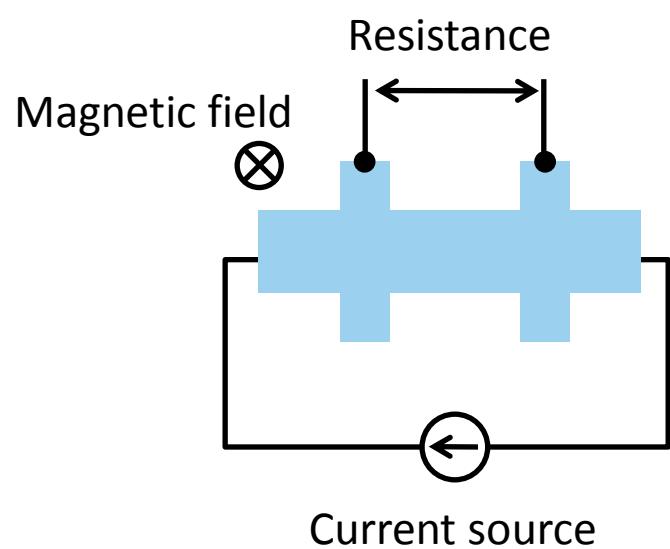
Magnetic field: 7.5 T

Hayakawa et al., Nature Nano. (2013)

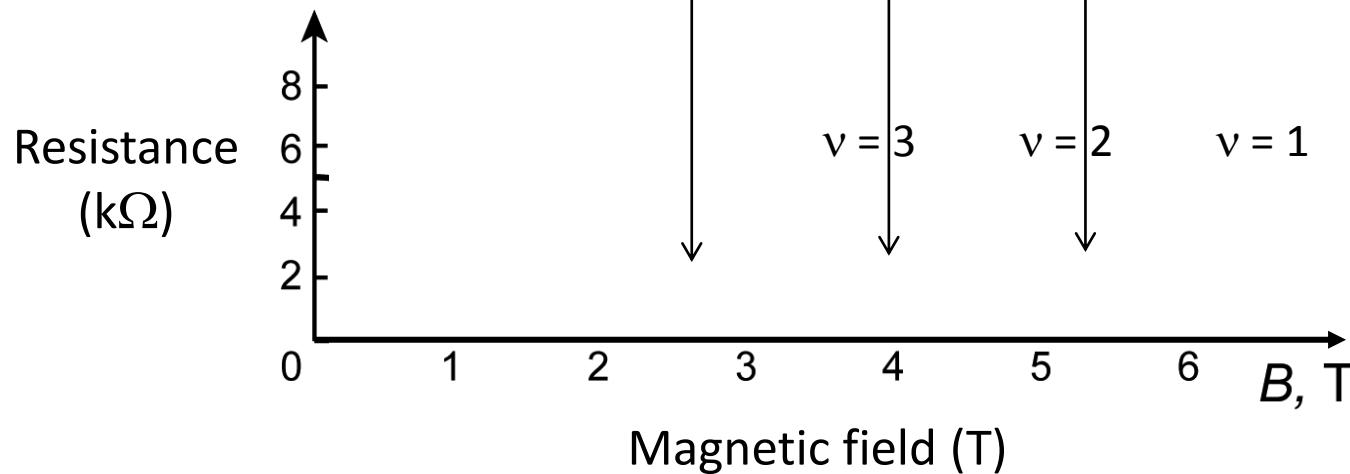
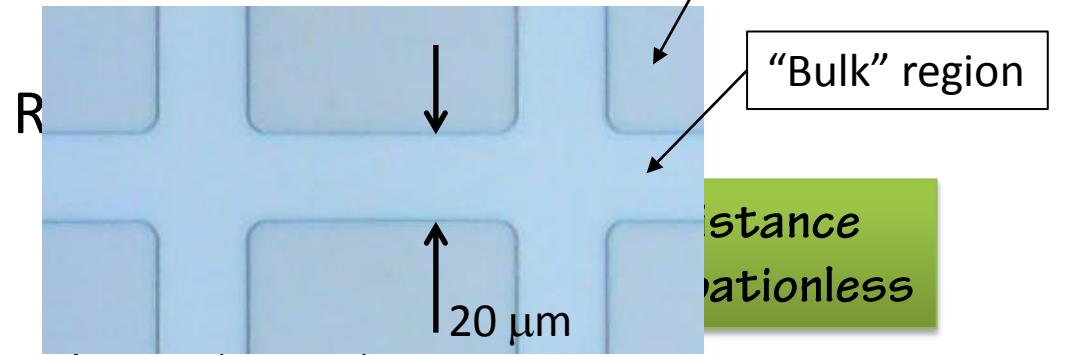
Mesa structure and sample edge



Quantum Hall effect

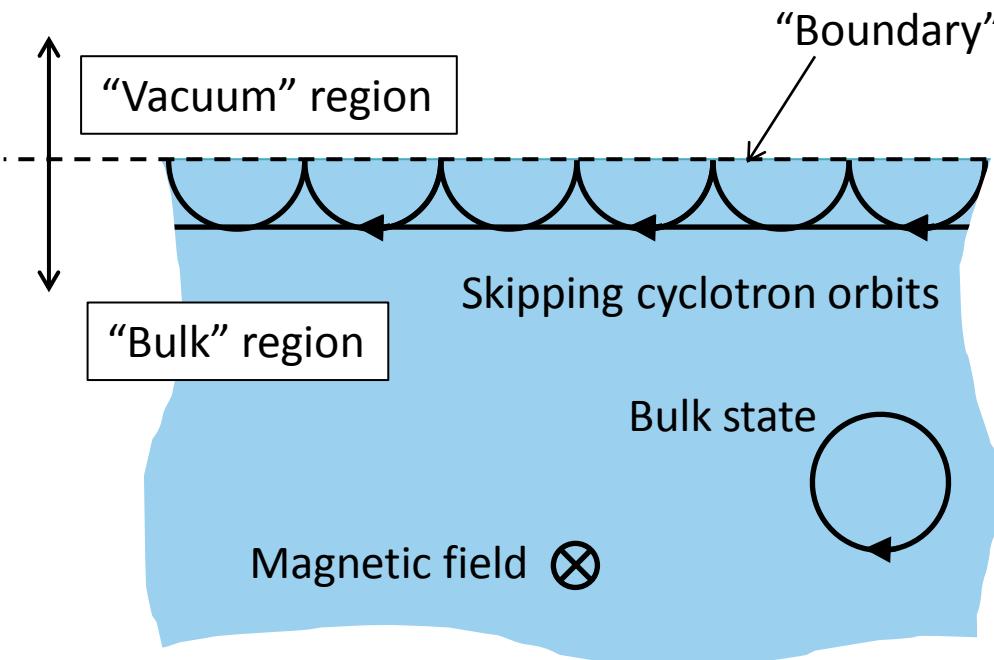


Optical microscope image
of a Hall bar



Top view

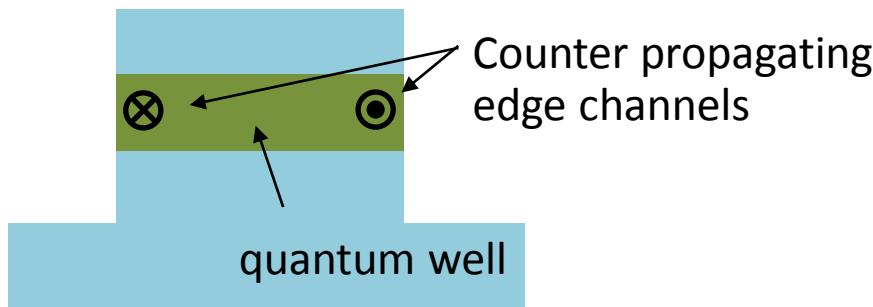
Edge state



Magnetic length $l_B = 8 \text{ nm}$
@ magnetic field $B = 10 \text{ T}$

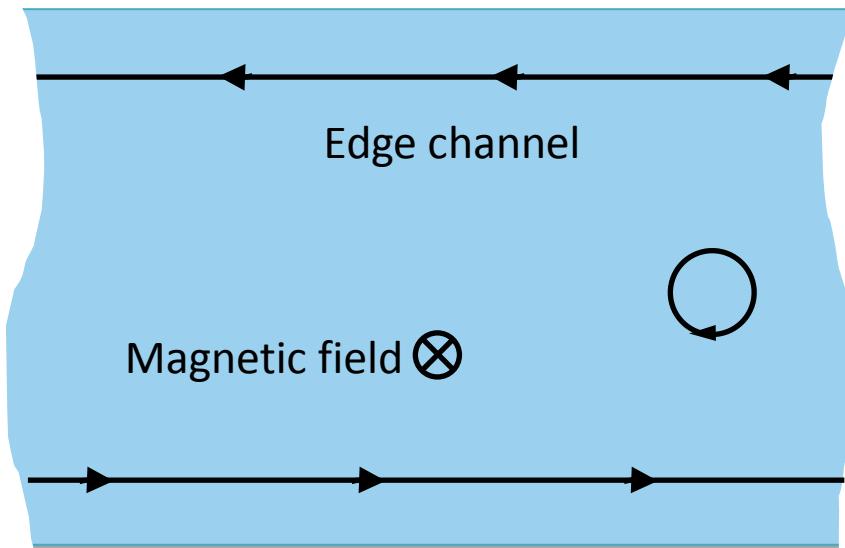
Skipping cyclotron orbits can be seen as quasi-one-dimensional channel. Such an edge channel behaves as a Chiral Luttinger liquid, along which current flows unidirectionally.

Cross sectional view



Edge state

"Moving walkways"



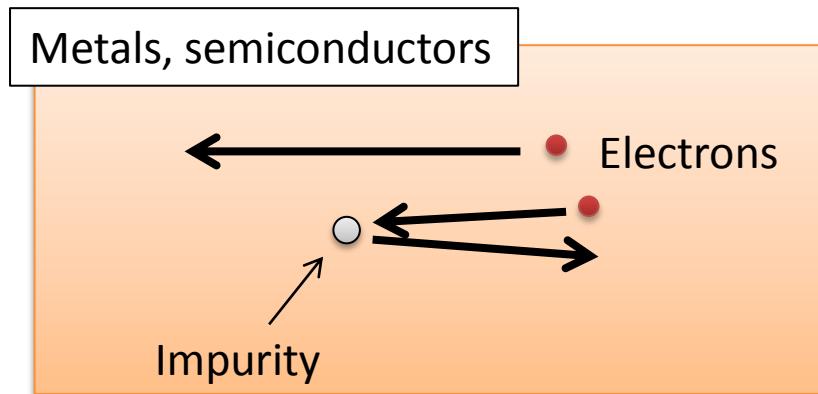
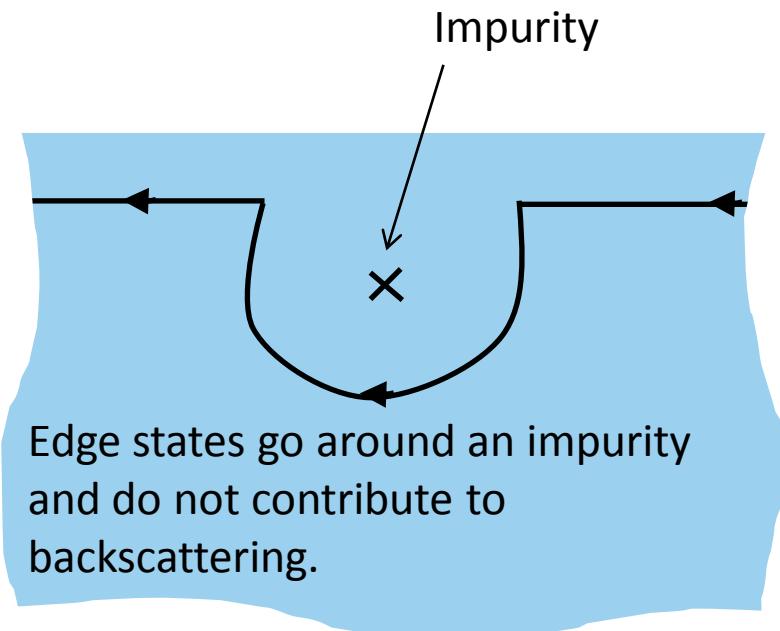
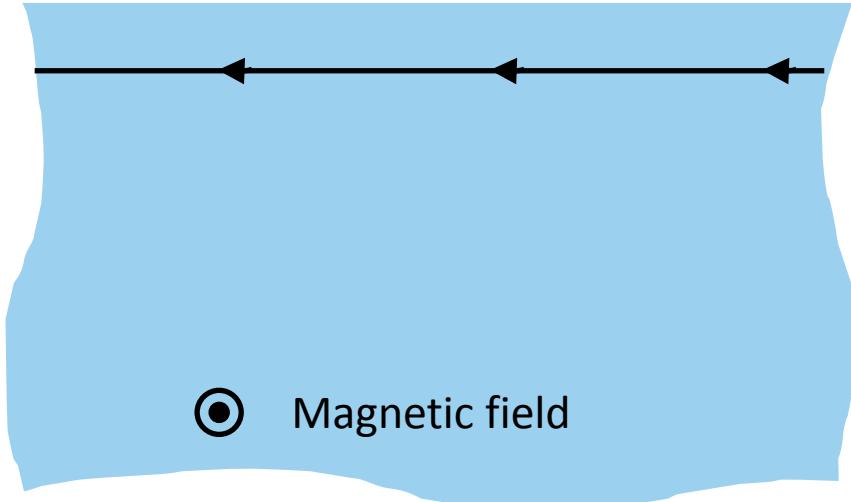
Unidirectional

The chiral field operator in terms of density field $\varrho_S(x)$
Commutation relation

$$[\varrho_S(x), \varrho_S(x')] = i \frac{\nu}{2\pi} \partial_x \delta(x - x')$$

Chiral (unidirectional) massless field in one dimension

Edge state



No backscattering
=> Zero-resistance

Requirements to verify QET

(1) Dissipationless system

Zero-resistance

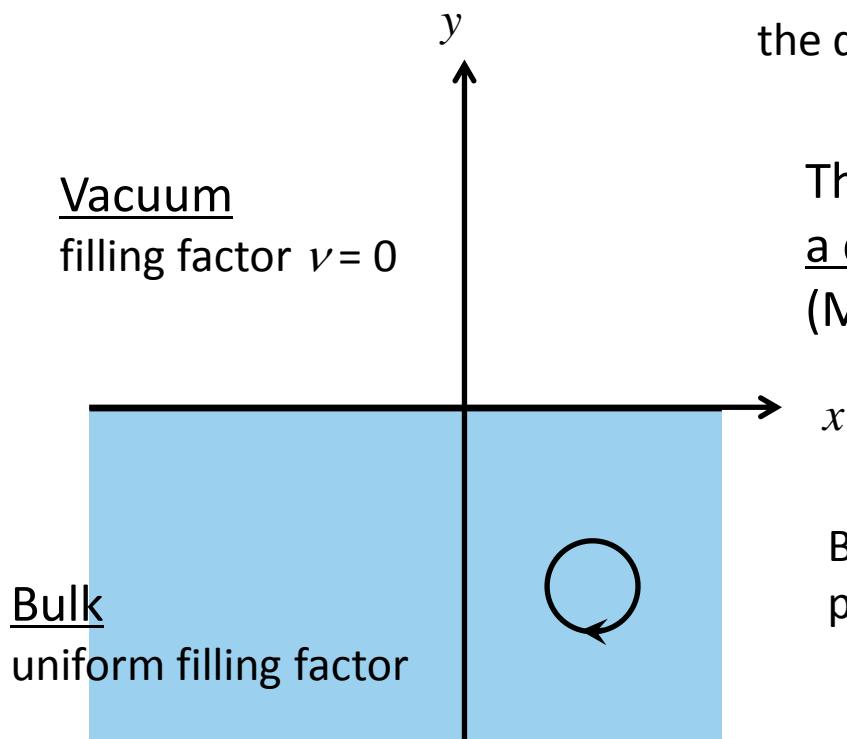
(2) Quantum correlation channel with macroscopic correlation length

(3) Detection and operation schemes for well-defined fluctuations in the vacuum state

(4) Suitable implementation of local operations and classical communication (LOCC)

The ground state and excitation of the edge state

Quasitachimagnetic at the edge
of the edge



Since the quantum Hall state is incompressible, the low-energy excitations are restricted to the deformation of the boundary.

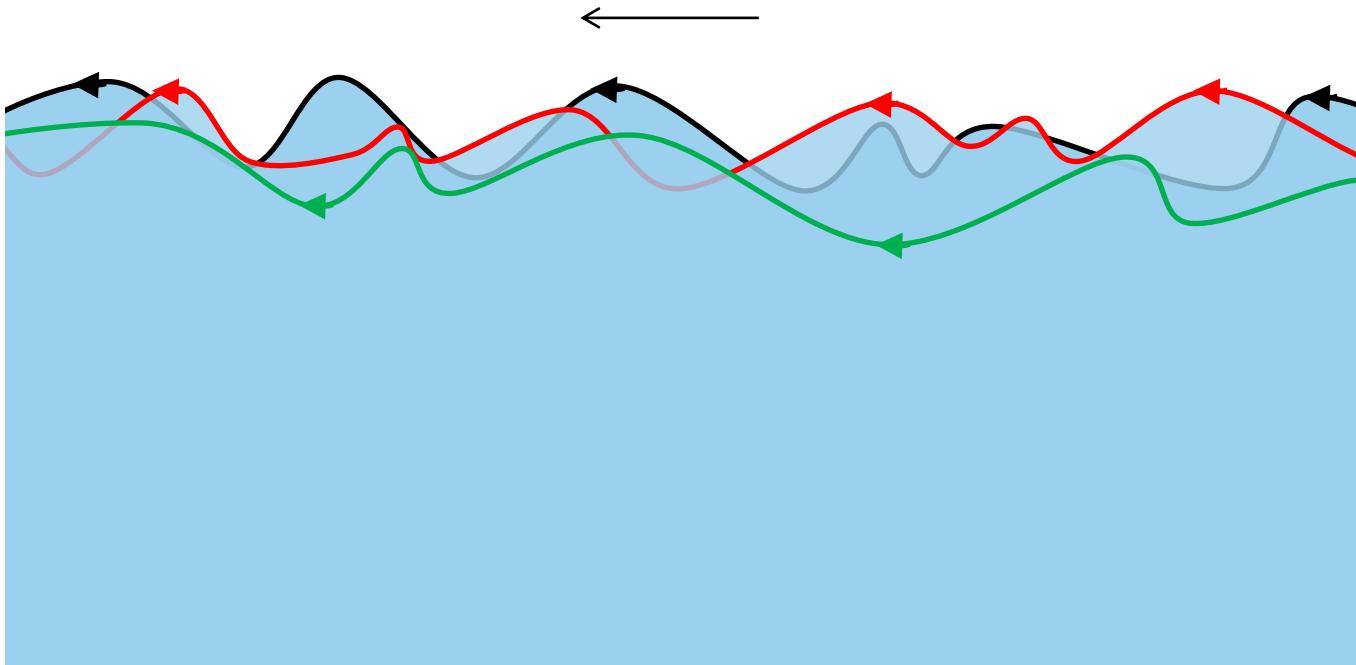
The excitation of the edge channel is
a deformation of the boundary.
(Magnetoplasmon)

By the Lorentz force a magnetoplasmon propagates with velocity

$$\nu_g = \frac{E}{B} \quad E: \text{the confining electric field}$$

The ground state of the edge state

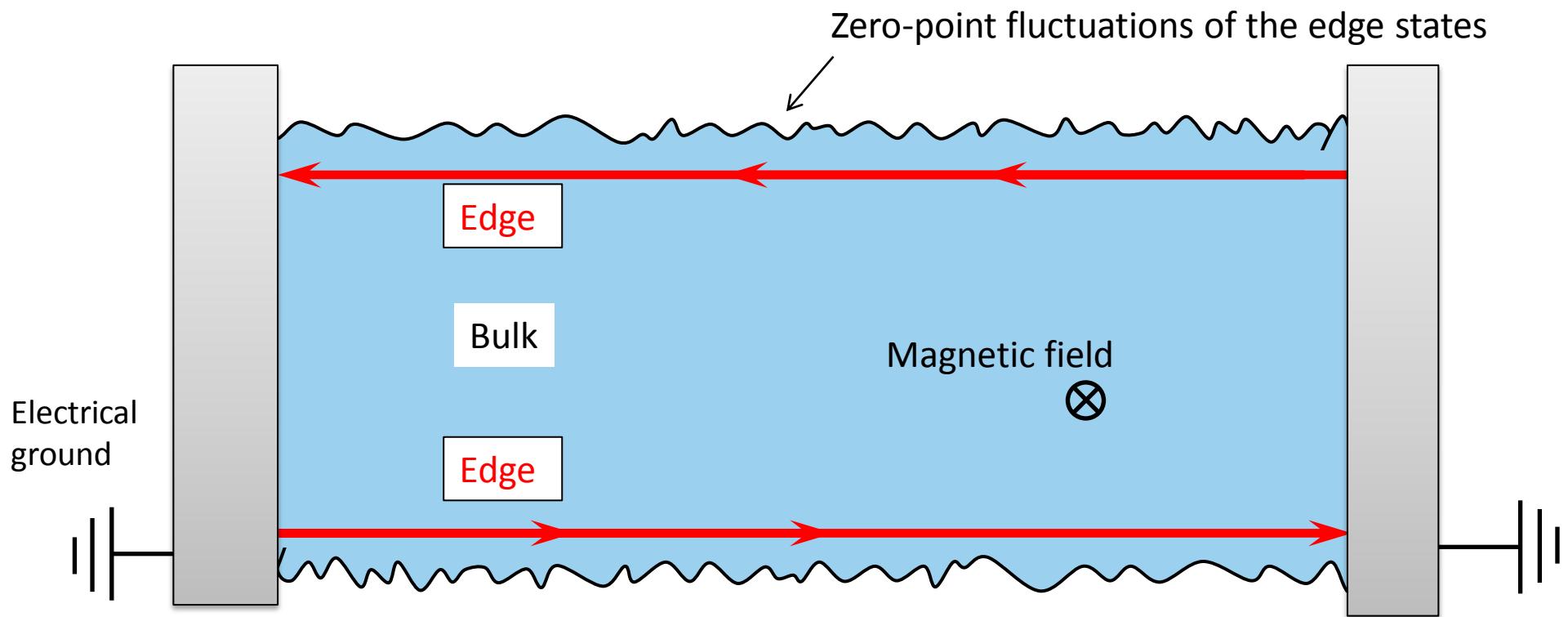
Zero-point fluctuations are superpositions of all possible patterns of deformed boundaries.



How to prepare the “vacuum” state

- The system is cool down the extent possible.
(The system is connected to the electrical ground.)
- No current or voltage is applied to the system.

The vacuum fluctuation of the edge state is the charge fluctuation



Requirements for verifying QET

✓ (1) Dissipationless system

Zero-resistance

✓ (2) Quantum correlation channel with macroscopic correlation length

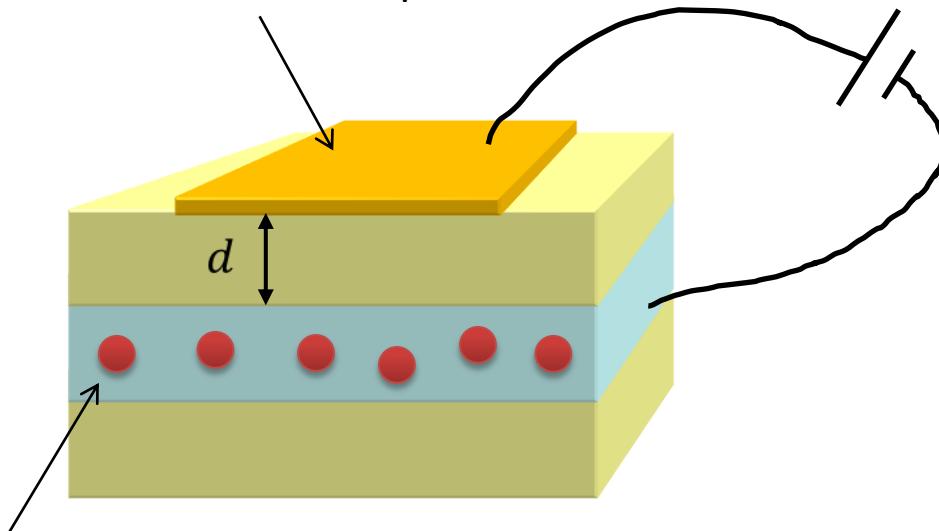
Edge channel

(3) Detection and operation schemes for well-defined fluctuations in the vacuum state

(4) Suitable implementation of local operations and classical communication (LOCC)

How to detect charge fluctuations

Thin metal film deposited on the surface of the sample



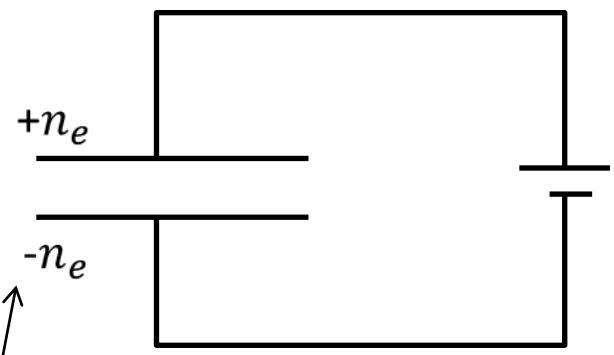
2D electron
 n_e : 2D electron density

Voltage source

Equivalent circuit

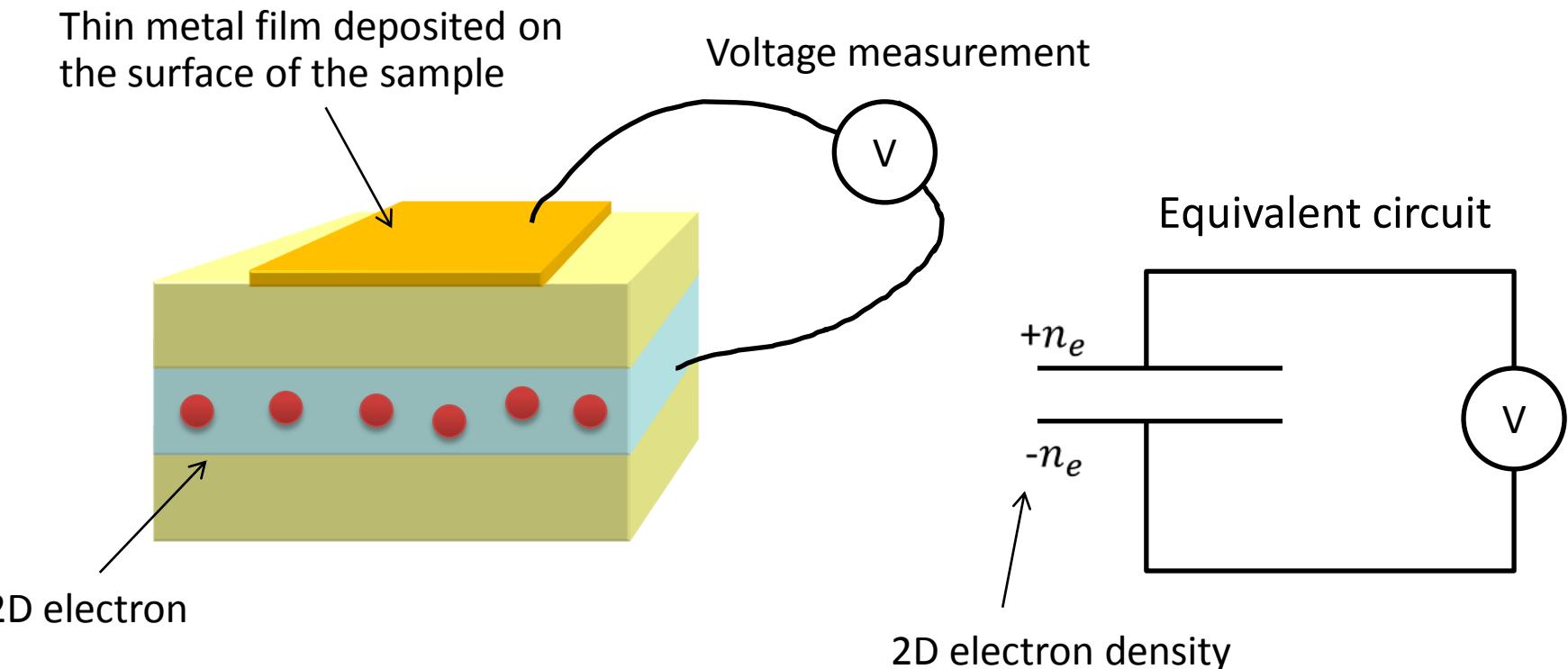
2D electron density

$$n_e = \frac{\epsilon_r \epsilon_0}{d} V$$



2D electrons + surface metal = parallel-plate capacitor

How to detect charge fluctuations

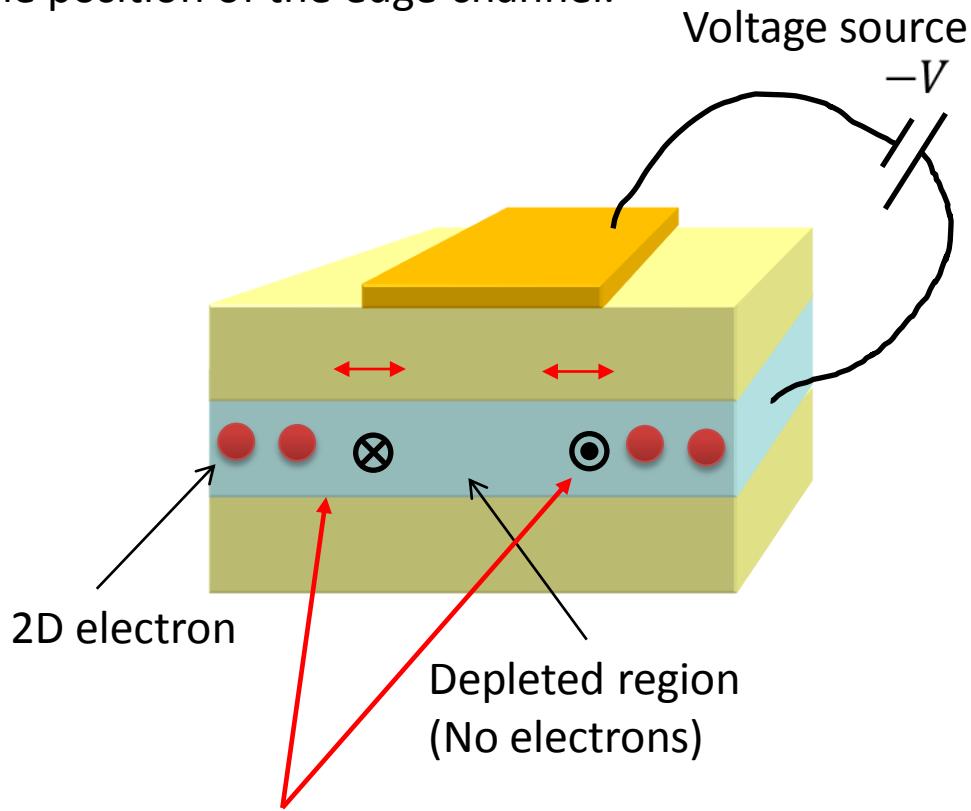


2D electrons + surface metal = parallel-plate capacitor

Measurement result = Voltage signal
An RC circuit is used as the detector.

Electrically controlled Edge channel

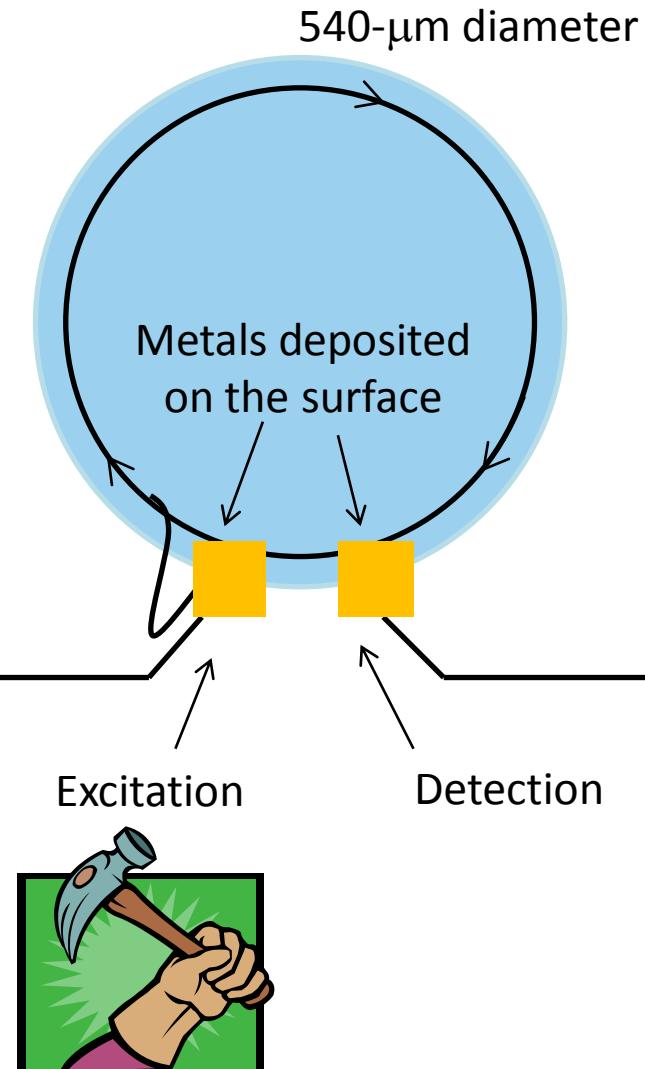
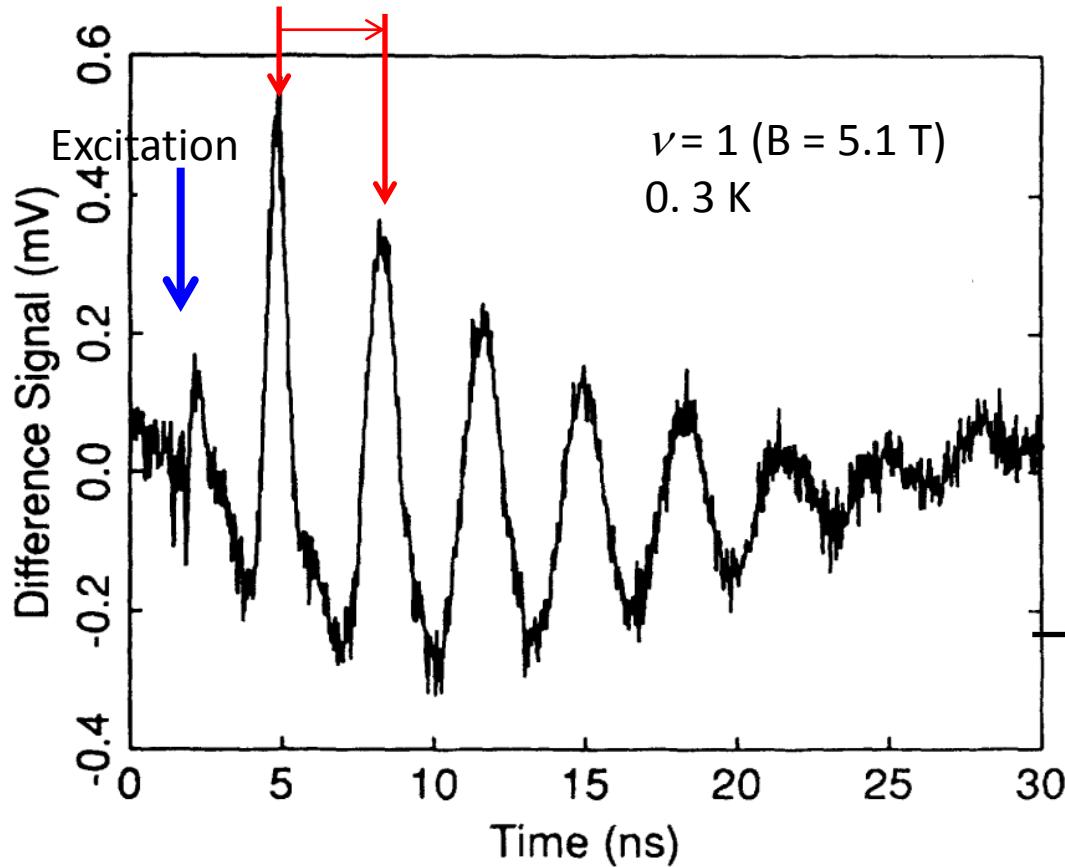
Electric field produced by the gate metal electrode can control electron density and the position of the edge channel.



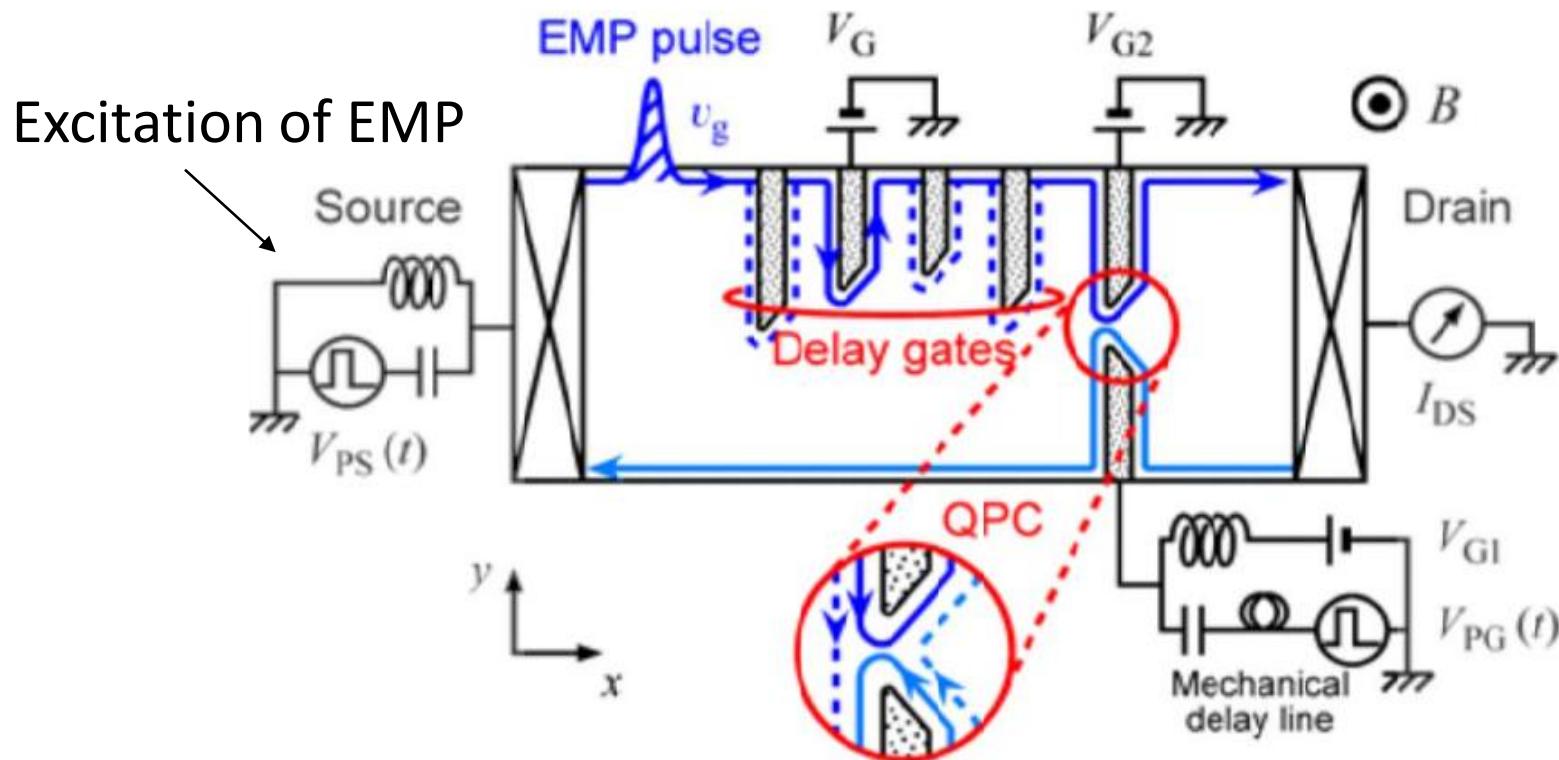
Edge channels are formed at this region
and the position of the edge can be
electrically controlled.

Excitation of the edge state edge magnetoplasmon (EMP)

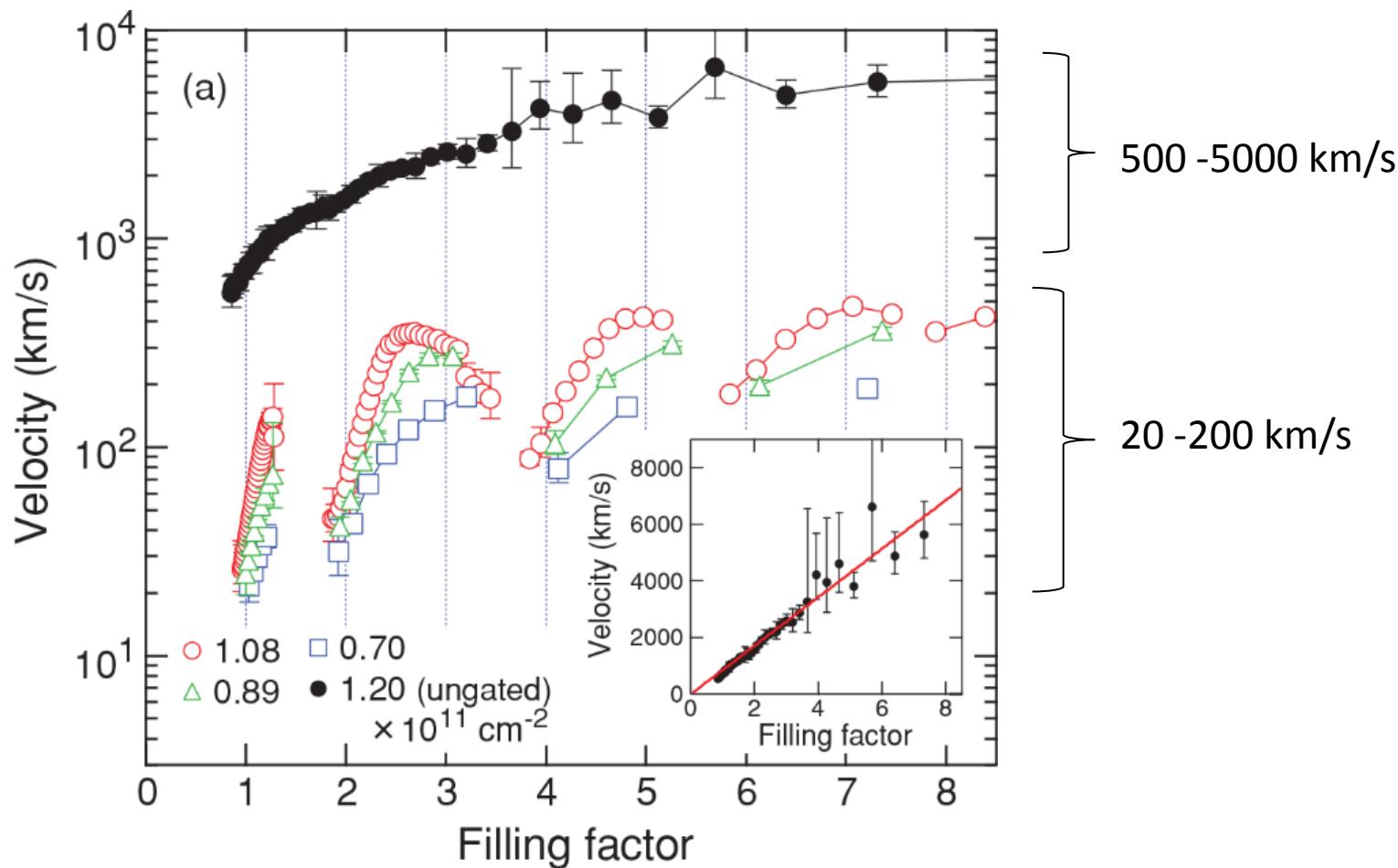
Time period for a wavepacket (magnetoplasmon) to complete circling around the sample once.



Propagation of Edge Magnetoplasmon (EMP)



Velocity of EMP



Requirements for verifying QET

✓ (1) Dissipationless system

Zero-resistance

✓ (2) Quantum correlation channel with macroscopic correlation length

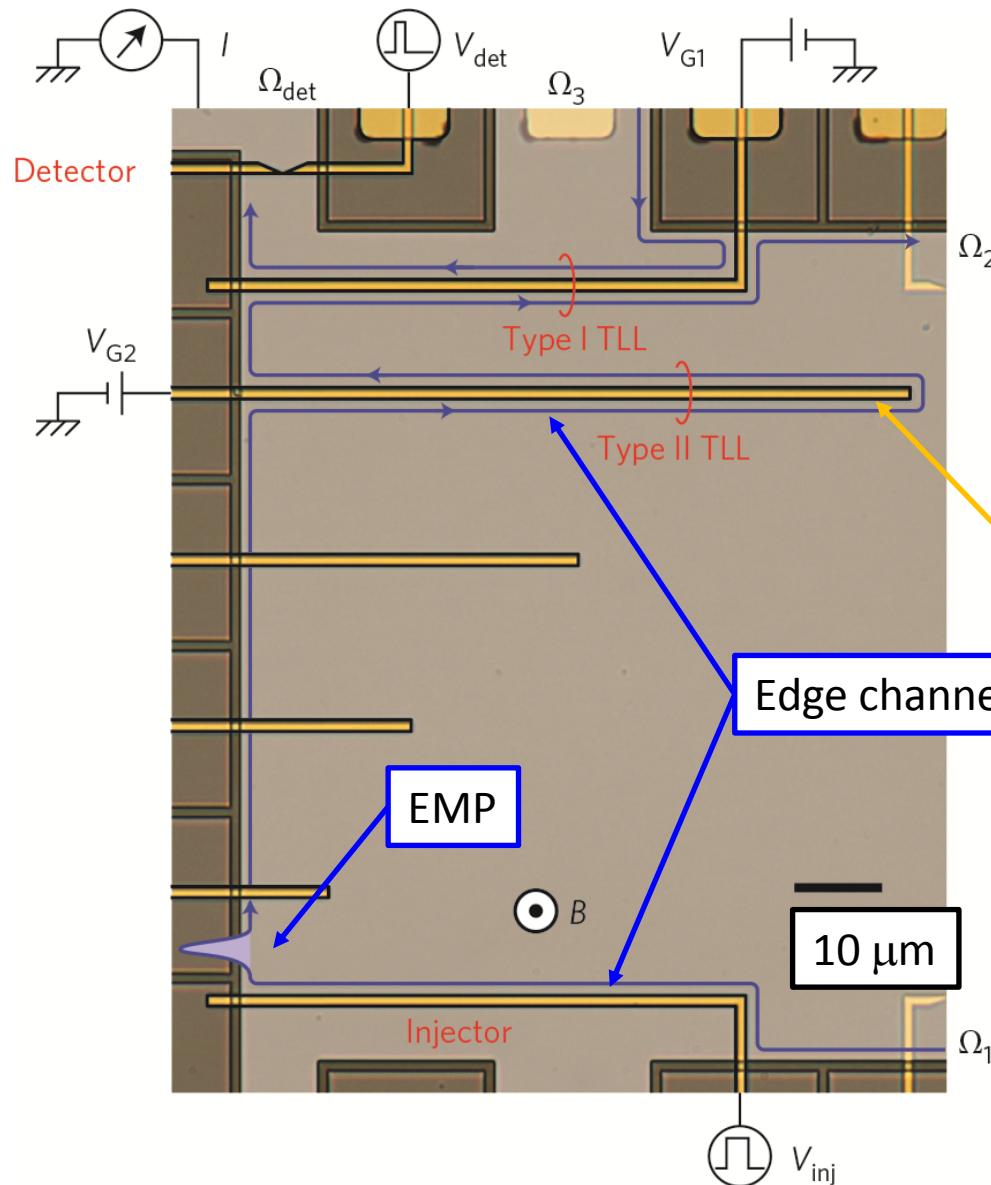
Edge channel

✓ (3) Detection and operation schemes for well-defined fluctuations in the vacuum state

RC circuit for charge fluctuations

(4) Suitable implementation of local operations and classical communication (LOCC)

Typical circuit to manipulate EMP



EMP (Edge magnetoplasmon) is the excitation of the edge channel.

Metal gate electrode

(To manipulate edge channels)

By using electron beam lithography
< 100-nm-scale structures can be
easily fabricated.

Requirements for Verifying QET

✓ 1) Dissipationless system

Zero-resistance

✓ 2) Quantum correlation channel with macroscopic correlation length

Edge channel

✓ 3) Detection and operation schemes for well-defined fluctuations in the vacuum state

RC circuit for charge fluctuations

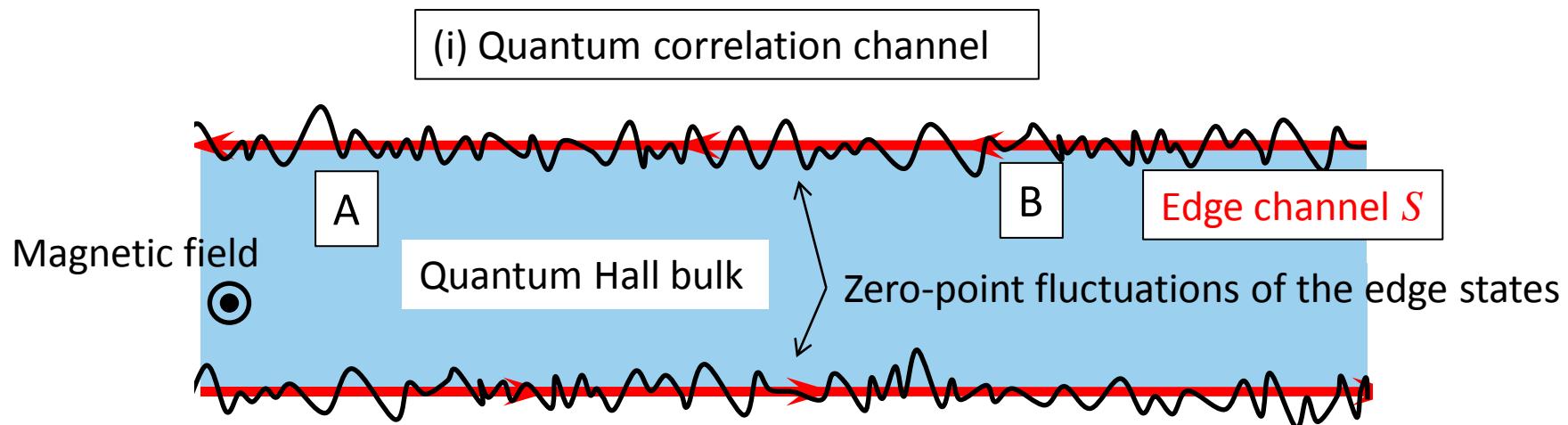
✓ 4) Suitable implementation of local operations and classical communication (LOCC)

Nanotechnology

A quantum Hall system is very suitable for verifying QET protocol.

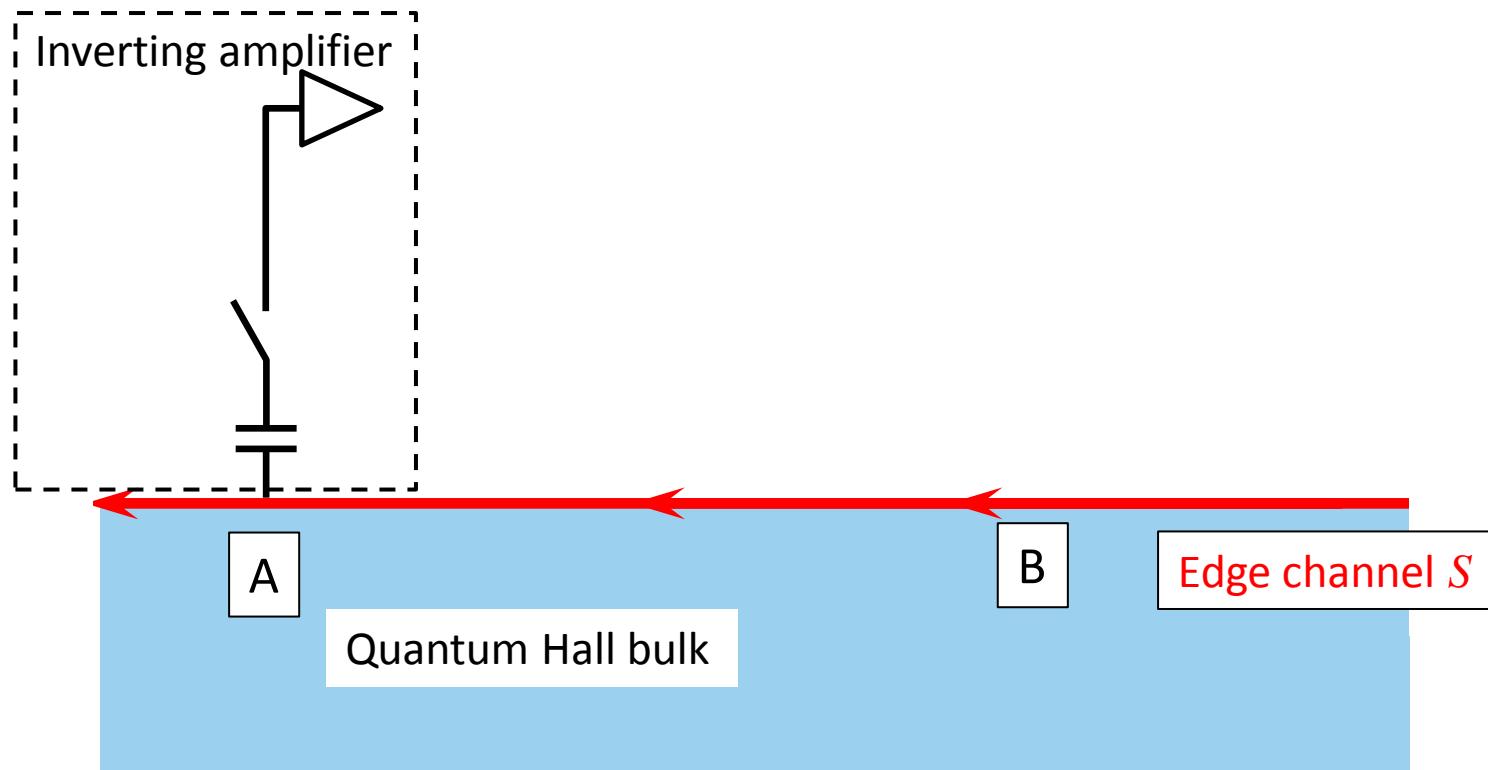
Schematic of the quantum Hall system for verifying quantum energy teleportation

The system should be cool down to the very low temperature. (\sim mK)



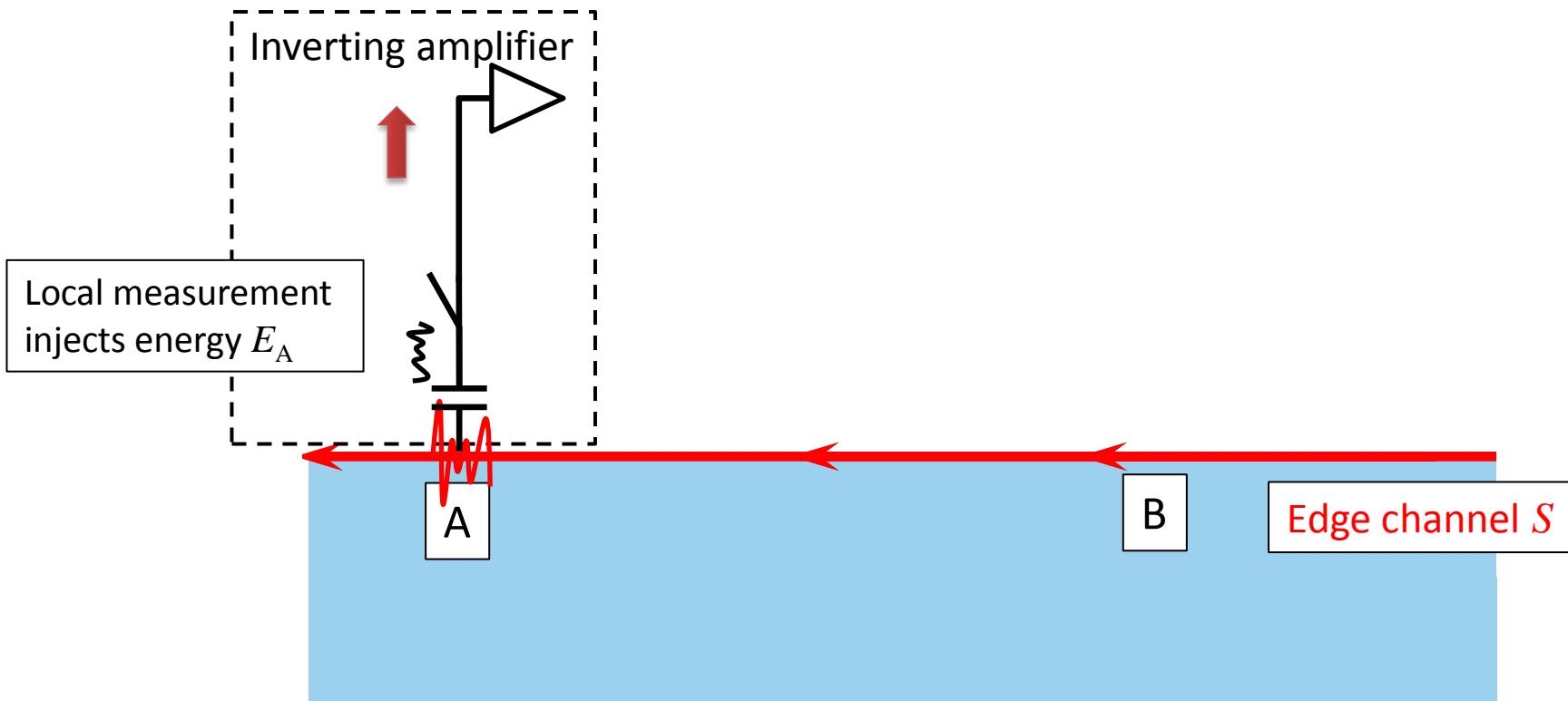
Schematic of the quantum Hall system for verifying quantum energy teleportation

(ii) Local measurement

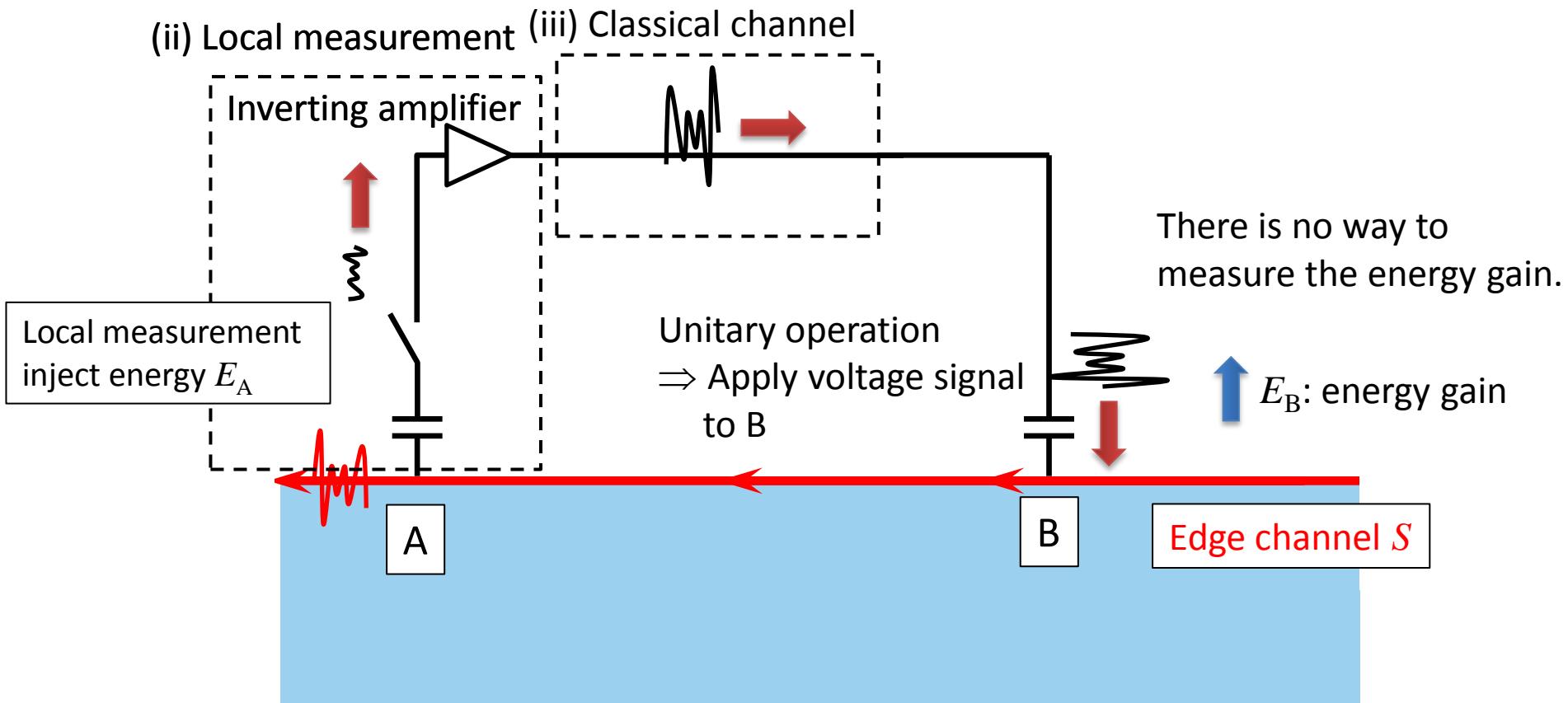


Schematic of the quantum Hall system for verifying quantum energy teleportation

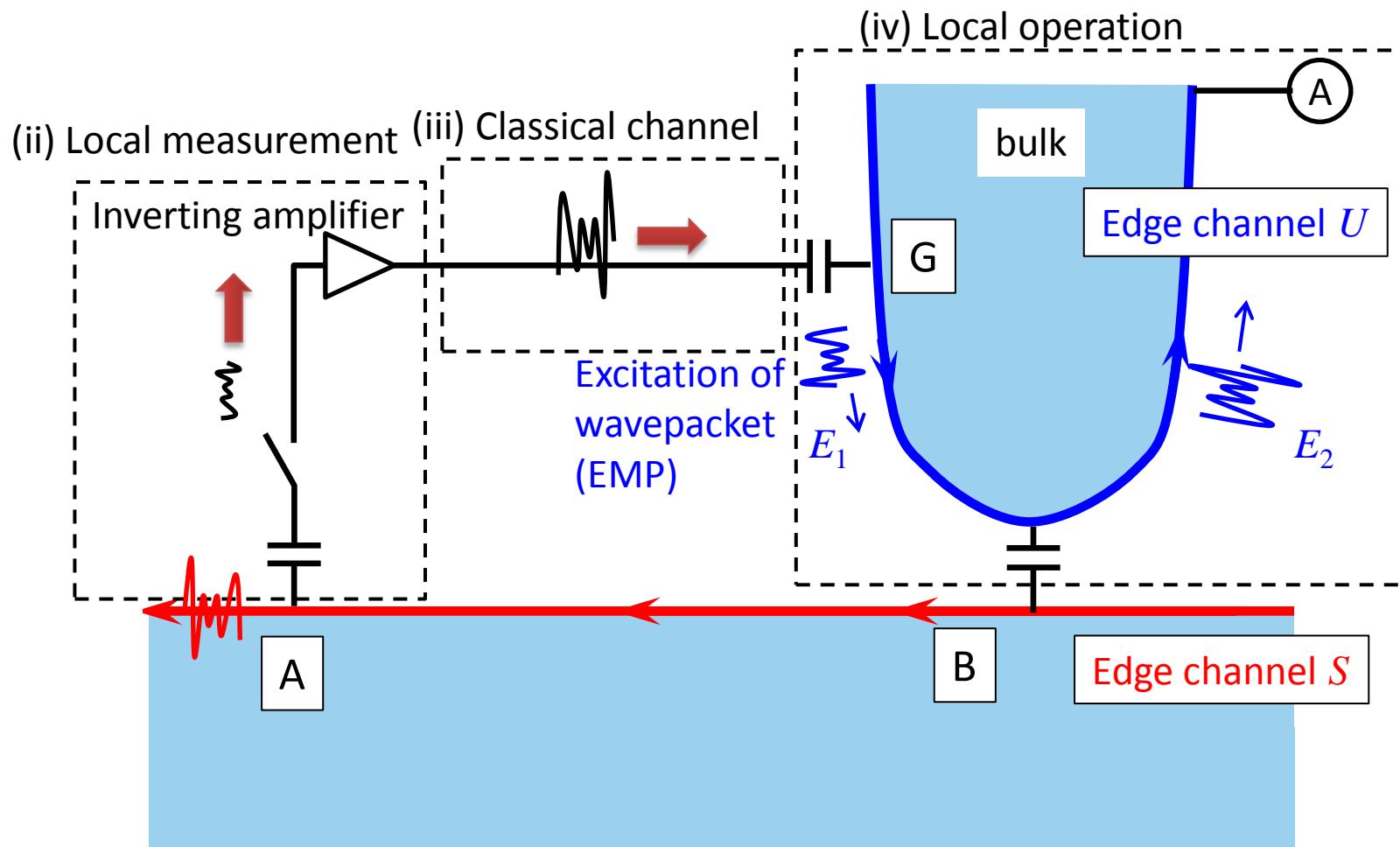
(ii) Local measurement



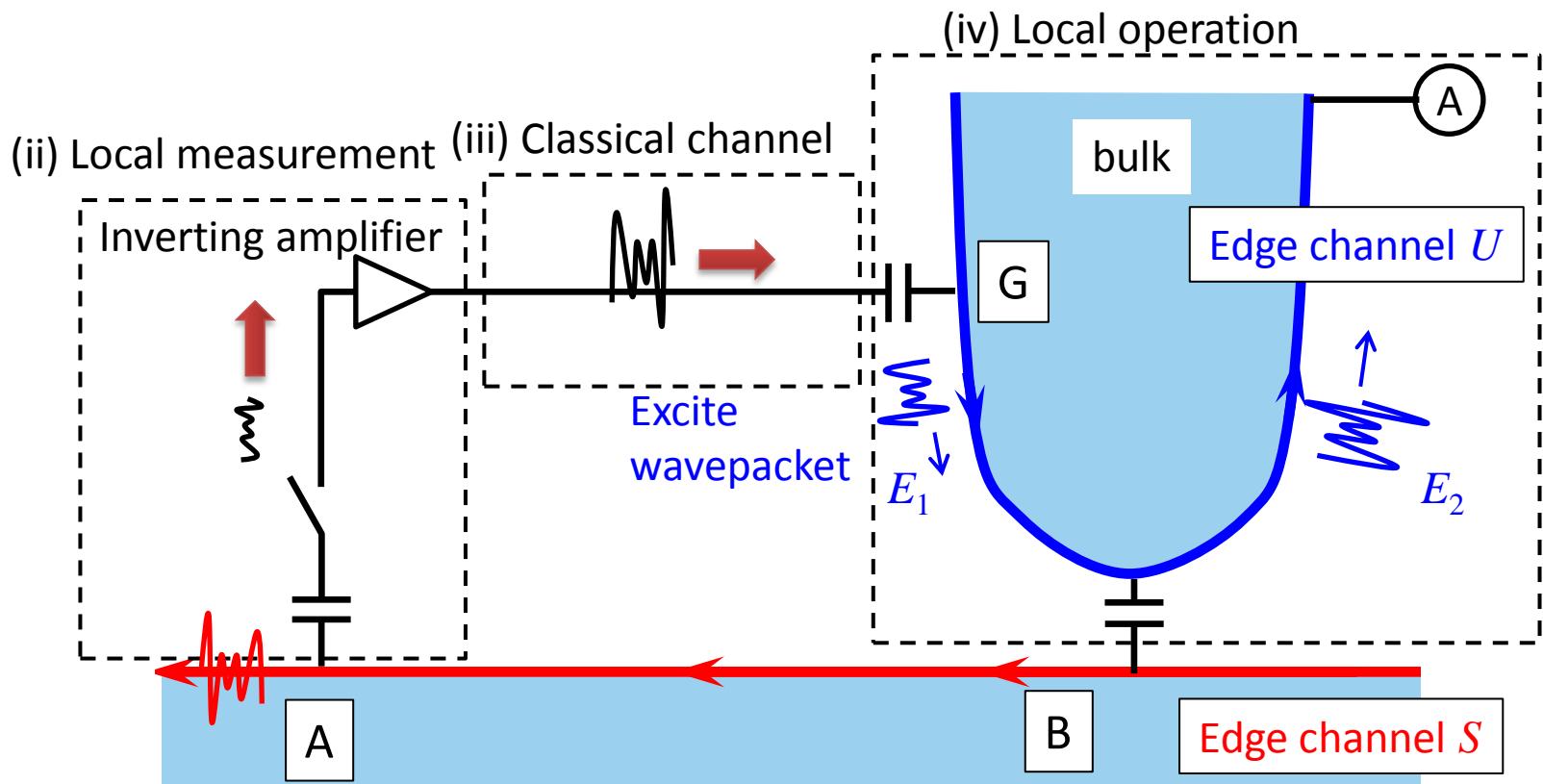
Schematic of the quantum Hall system for verifying quantum energy teleportation



Schematic of the quantum Hall system for verifying quantum energy teleportation



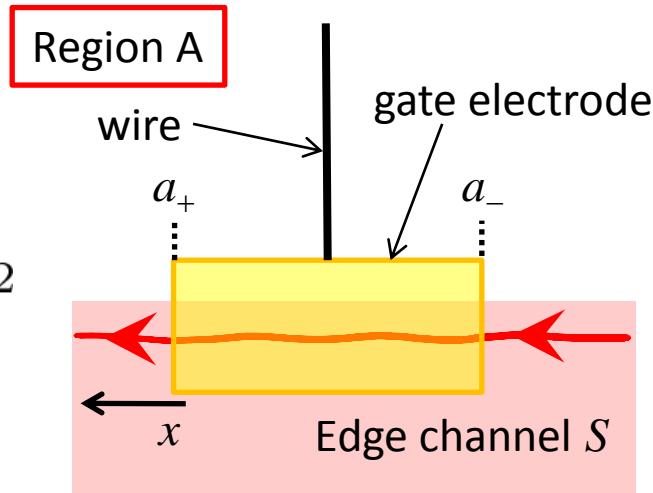
Schematic of the quantum Hall system for verifying quantum energy teleportation



1. The wavepacket (=EMP) is created at G by the voltage signal (measurement result) and propagates with energy E_1 .
 2. The wave packet interacts with Edge channel S at B.
 3. The energy carried by the wavepacket changes from E_1 to E_2 .
- If $E_2 - E_1 (= E_B)$ is positive, energy E_B is extracted from the local vacuum state!

E_A : Energy infused by the local measurement

$$E_A = \frac{\hbar v_g \nu_S}{4\pi} \left(\frac{ev_g R}{2\Delta V} \right)^2 \int_{-\infty}^{\infty} dx \left(\partial_x^2 w_A(x) \right)^2$$



ν_S : Filling factor at edge channel S ($= 3$)

v_g : group velocity of the edge channel, $v_g \sim 10^6$ m/s

R : resistance 10 k Ω

ΔV : amplitude of the quantum noise of the voltage signal

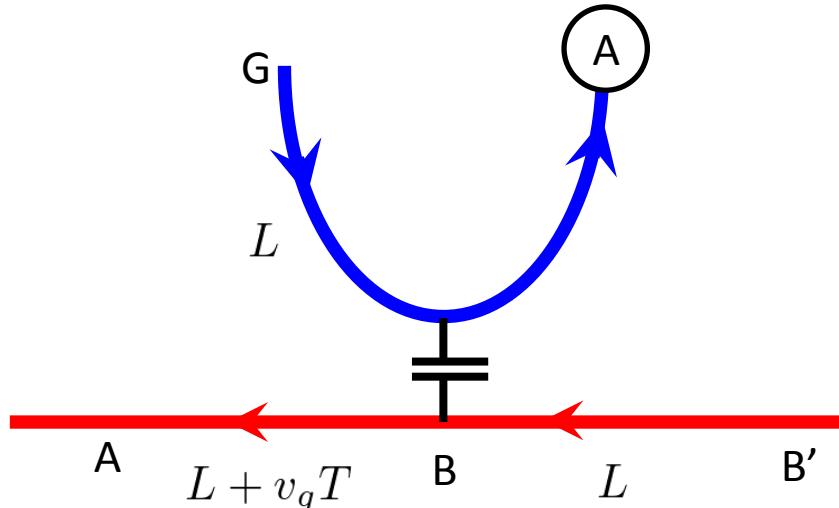
$$\Delta V \sim \sqrt{\frac{\hbar}{RC^2}} \sim 10 \text{ } \mu\text{V}$$

$w_A(x)$: a window function which equal to ~ 1 at A $x \in [a_-, a_+]$

$$E_A \sim 1 \text{ meV}$$

E_B : The extracted energy at B

$$E_B \sim \frac{e^2 \lambda_B}{4\pi\epsilon l} \frac{ev_g R}{l\Delta V} \left(\frac{l}{L}\right)^5$$



L : ~the distance between A and B

l : the size of the gate ($10 \mu\text{m}$)

ϵ : dielectric constant of the host semiconductor

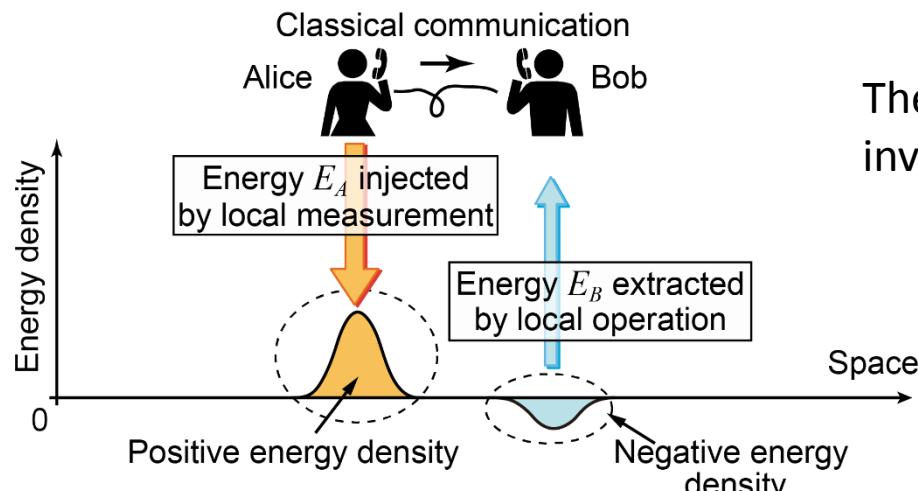
λ_B : a window function related to the total number of excited electrons and quasi holes from the vacuum state ($= 10$)

T : the time period for the classical signal to travel from A to G

- All positive parameters guarantee positive E_B .
- $E_B \sim 100 \mu\text{eV}$ for $L \sim 2l$ (\gg thermal energy $\sim 1 \mu\text{eV}$ at 10 mK)
This means that energy is extracted at a distance of $\sim 2L$ ($\sim 4l = 40 \mu\text{m}$).
- Extension of L rapidly degrades magnitude of E_B .
e.g., $E_B \sim 1 \mu\text{eV}$ for $L \sim 4l$
- Since E_B is not maximized, much more energy gain can be expected.

Long distance QET

(a) Vacuum state QET



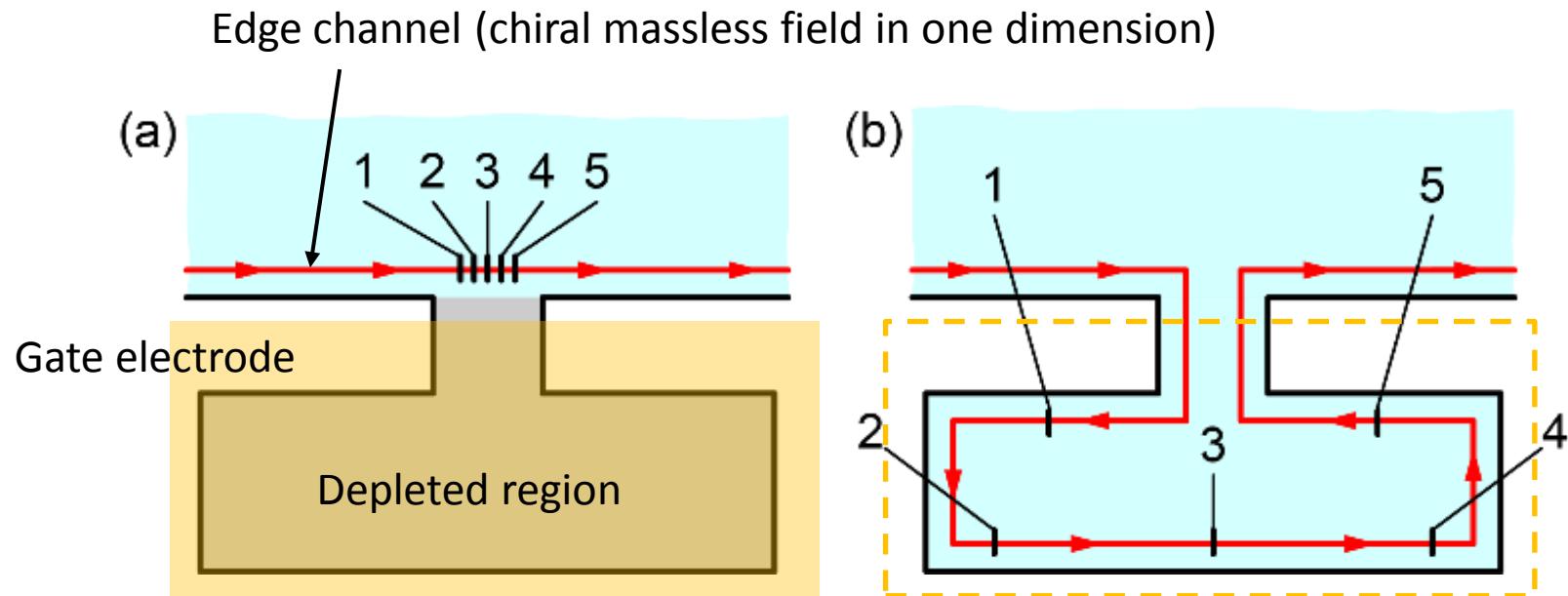
The upper bound of the energy being inversely proportional to the distance.

$$E_B \leq \frac{1}{12\pi L} \quad \begin{aligned} L &: \text{distance} \\ \text{The natural unit} \\ (C = \hbar = 1) \end{aligned}$$

Introducing squeezed vacuum states with local vacuum regions between A and B overcomes the limitation of distance.

Spatial expansion method

A local extrusion of bulk electrons toward the outside can be experimentally obtained by dynamically controlling the electron density in the depleted region.



Experimental progress

Dilution refrigerator

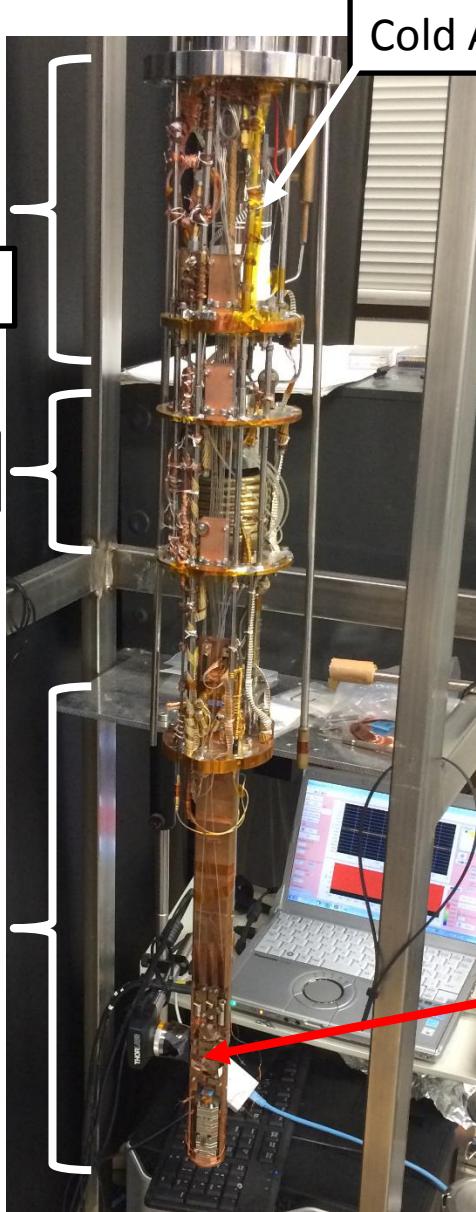
provides continuous cooling down to mK region using He³ and He⁴ isotopes.

4 K

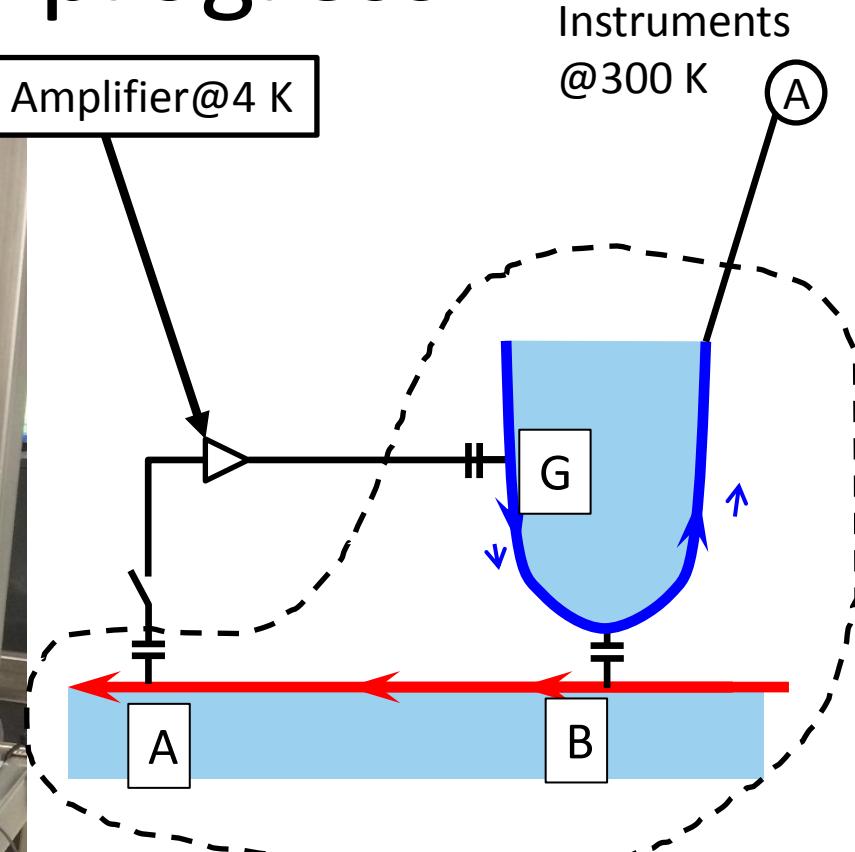
<2 K

40 mK

Min temperature ~ 40 mK
Max magnetic field 16 T



Cold Amplifier@4 K



Instruments
@300 K

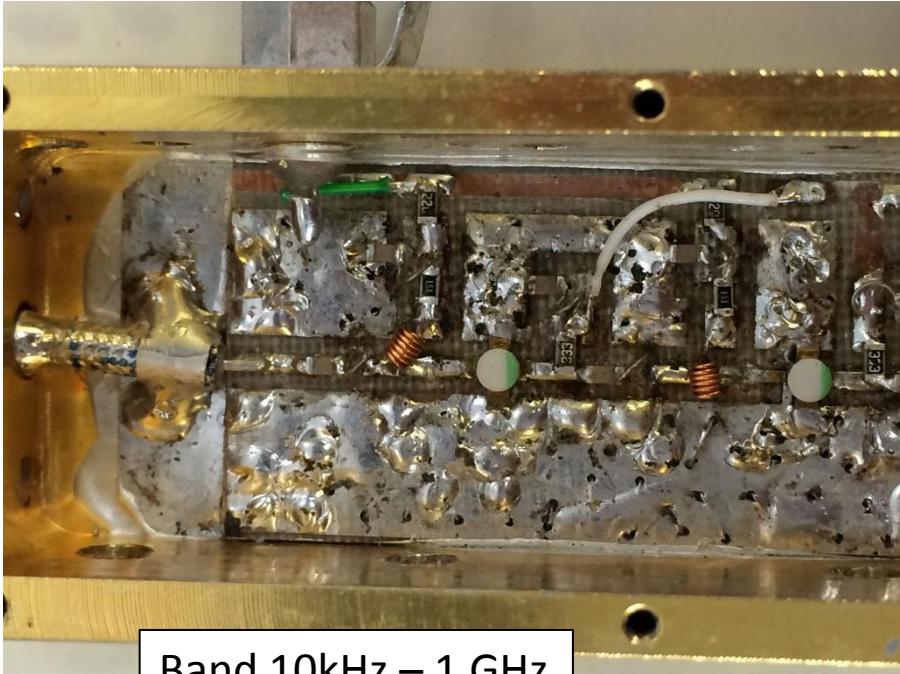
(A)

Device@40 mK

We sink the whole dilution unit
into liquid helium bath (4 K).

Low noise amplifier operating at 4 K cryo amplifier

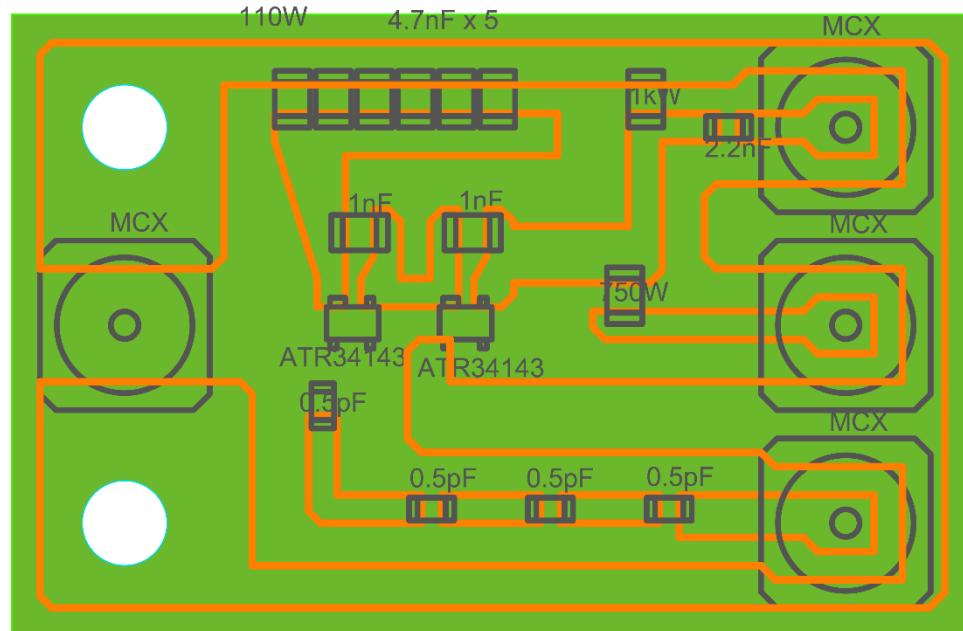
Example of cyro amp.



Band 10kHz – 1 GHz
Gain 20 (dB)
Noise Figure 1 dB

Still have some problem with heating.

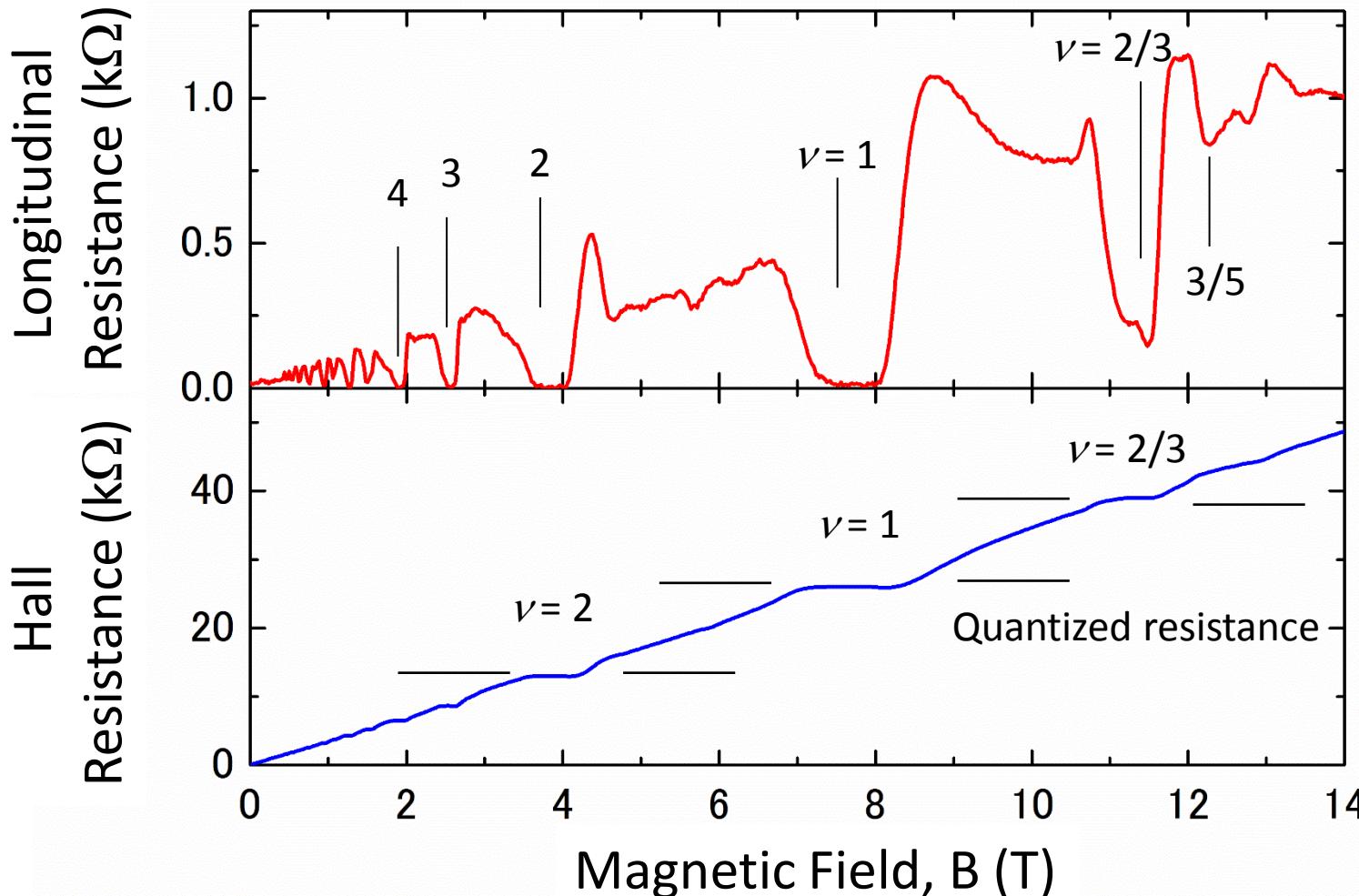
Example of circuit diagram of cyro amp.



Quality of semiconductor wafers

The wafer is processed into a Hall bar structure.

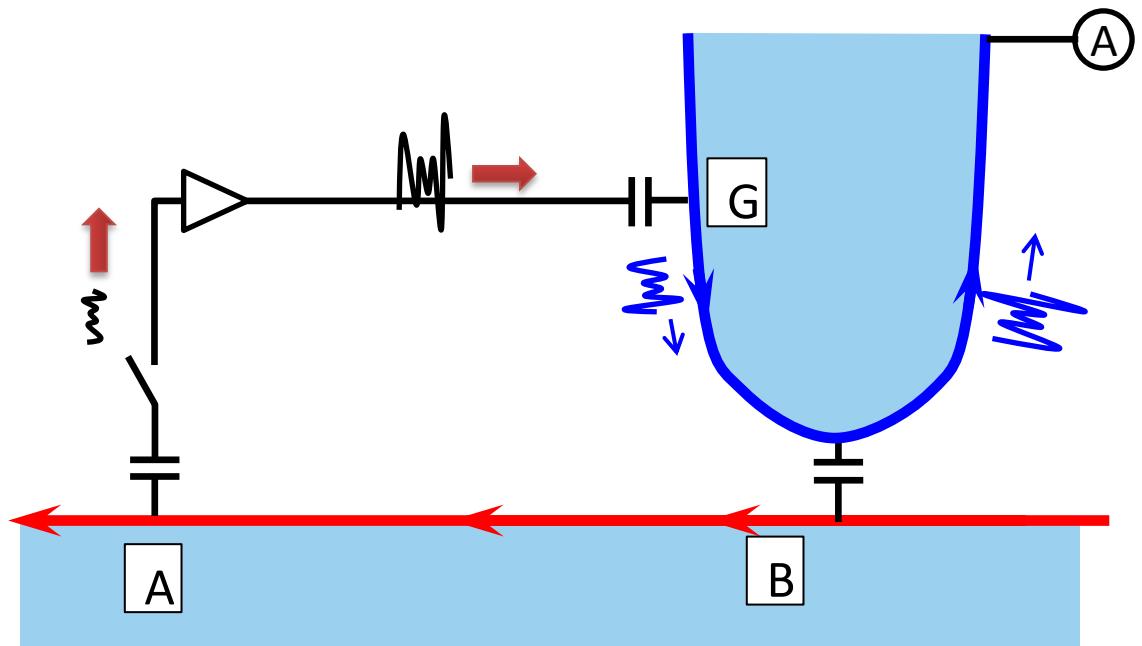
Four terminal measurement was performed using lock-in amplifier.



The wafer is provided from National Institute for Material Science (NIMS).

Summary

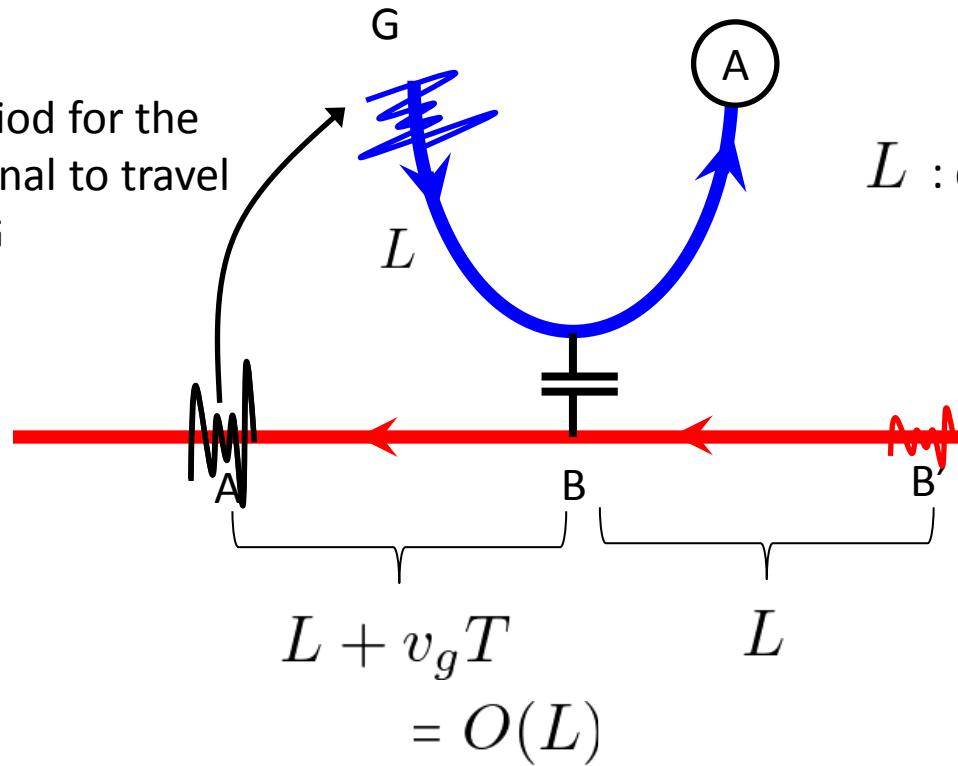
- We have theoretically implemented a quantum energy protocol (quantum energy teleportation).
- E_B is positive and is estimated to be the order of $\sim 100 \mu\text{eV}$ at a distance of $40 \mu\text{m}$.
(= 4000 times of the size of an electron)



Effective “teleported” distance

T : time period for the classical signal to travel from A to G

L : distance from G to B



Since the wavepacket created at G interacts with the local vacuum state originally located at B', the effective “teleported” distance is not L but $\sim 2L$.

E_B : The extracted energy at B

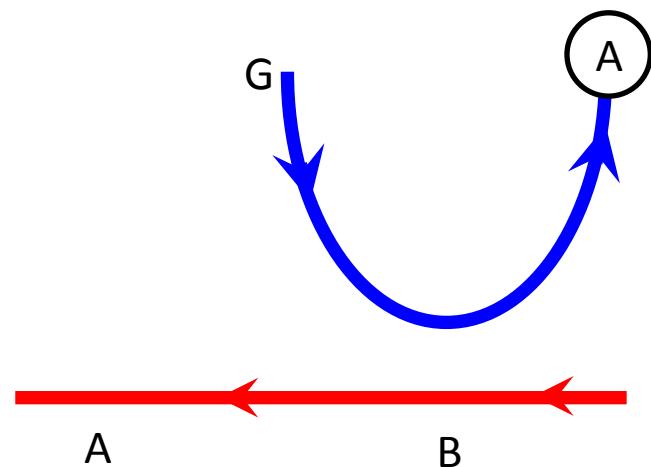
$$E_B \sim \frac{e^2 \lambda_B}{4\pi\epsilon l} \frac{ev_g R}{l\Delta V} \left(\frac{l}{L}\right)^5$$

L : ~the distance between A and B

l : the size of the gate(10 μm)

ϵ : dielectric constant of the host semiconductor

λ_B : a window function related to the total number of excited electrons and quasi holes from the vacuum state (= 10)



- All positive parameters guarantee positive E_B .
- $E_B \sim 100 \mu\text{eV}$ for $L \sim 2l$ (\gg thermal energy $\sim 1 \mu\text{eV}$ at 10 mK)
- Extension of L rapidly degrades magnitude of E_B .
(e.g., $E_B \sim 1 \mu\text{eV}$ for $L \sim 4l$)

The energy density

$$\varepsilon = \frac{\pi \hbar}{\nu_P e^2 v_g} j^2 \sim 10 \mu\text{eV}/\mu\text{m} \rightarrow \text{current } j \sim 10 \text{ nA}$$

ν_P : filling factor of the edge channel P

Experimental parameters we used

- Capacitance $C \sim 10 \text{ fF}$
- Input resistance $R \sim 10 \text{ k}\Omega$
- Typical group velocity of a charge density wave
 $v_g \sim 10^6 \text{ m/s}$
- Typical length scale $l \sim 10 \text{ }\mu\text{m}$
 - the length of regions A, B, and G
- Temperature $\sim \text{mK}$

Formulation of chiral edge channel S

The chiral field operator $\varrho_S(x)$

$$[\varrho_S(x), \varrho_S(x')] = i \frac{\nu_S}{2\pi} \partial_x \delta(x - x') \varrho_S(x)$$

The energy density operator of $\varrho_S(x)$

$$\varepsilon_S(x) = \frac{\pi \hbar v_g}{\nu_S} : \varrho_S(x)^2 :$$

ν_S : the Landau level filling factor of S

v_g : the group velocity of a charge density wave

:: denotes normal ordering which makes $\langle 0_S | \varepsilon_S(x) | 0_S \rangle = 0$

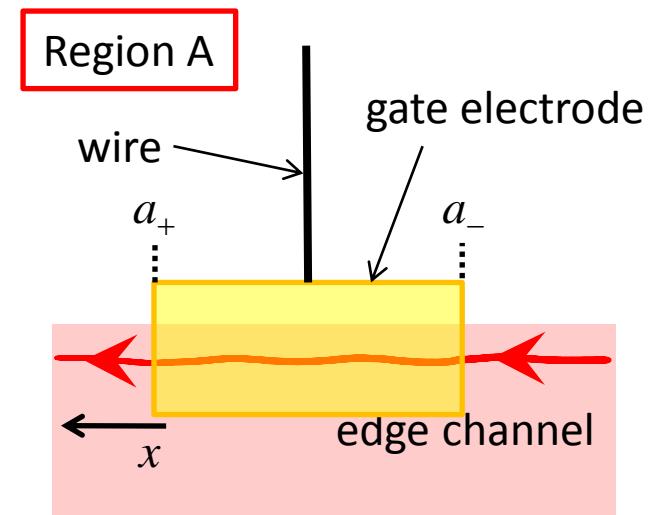
The free Hamiltonian of S :

$$H_S = \int_{-\infty}^{\infty} \varepsilon_S(x) dx \quad H_S |0_S\rangle = 0$$

The charge fluctuation at A

$$Q_S(t) = e \int_{-\infty}^{\infty} \varrho_S(x + v_g t) w_A(x) dx \quad (1)$$

$w_A(x)$: window function which equals to 1 in $x \in [a_-, a_+]$



Quantum noise of the voltage $V(t)$

$$\hat{V} = -\sqrt{\frac{\hbar}{\pi RC^2}} \int_0^\infty d\omega \left[\frac{\sqrt{\omega}}{\omega - \frac{1}{iRC}} a_{in}(\omega) + \frac{\sqrt{\omega}}{\omega + \frac{1}{iRC}} a_{in}^\dagger(\omega) \right] \quad (2)$$

$a_{in}(\omega)$ $a_{in}(\omega)^\dagger$: annihilation and creation operators of excitation of the charge density wave (magneto-plasmon)

Reference: G. Feve *et al.* Phys. Rev. B **77** 035308 (2008).

Voltage after the measurement

$$V(t = +0) = \hat{V} + \underline{R\dot{Q}_S(0)} \quad (3)$$

voltage shift induced by the signal

The amplitude of \hat{V}

$$\Delta V = \sqrt{\langle 0_{RC} | \hat{V}^2 | 0_{RC} \rangle} \sim \sqrt{\frac{\hbar}{RC^2}} \sim 10 \text{ } \mu\text{V}$$

The root mean square value of the voltage shift

$$\sqrt{\langle 0_S | \left(R\dot{Q}_S(0) \right)^2 | 0_S \rangle} \sim \underline{100 \text{ } \mu\text{V}} \quad \text{from Eq. (1)}$$

Quantum fluctuations of the edge channel is detectable

Formulation of local measurement

by pointer-basis of von Neumann

Measurement operator M_v of the macroscopic system with the output value of v

Measurement Hamiltonian

$$H_m(t) = \hbar\delta(t)R\dot{Q}_S(0)P_{\hat{V}}$$

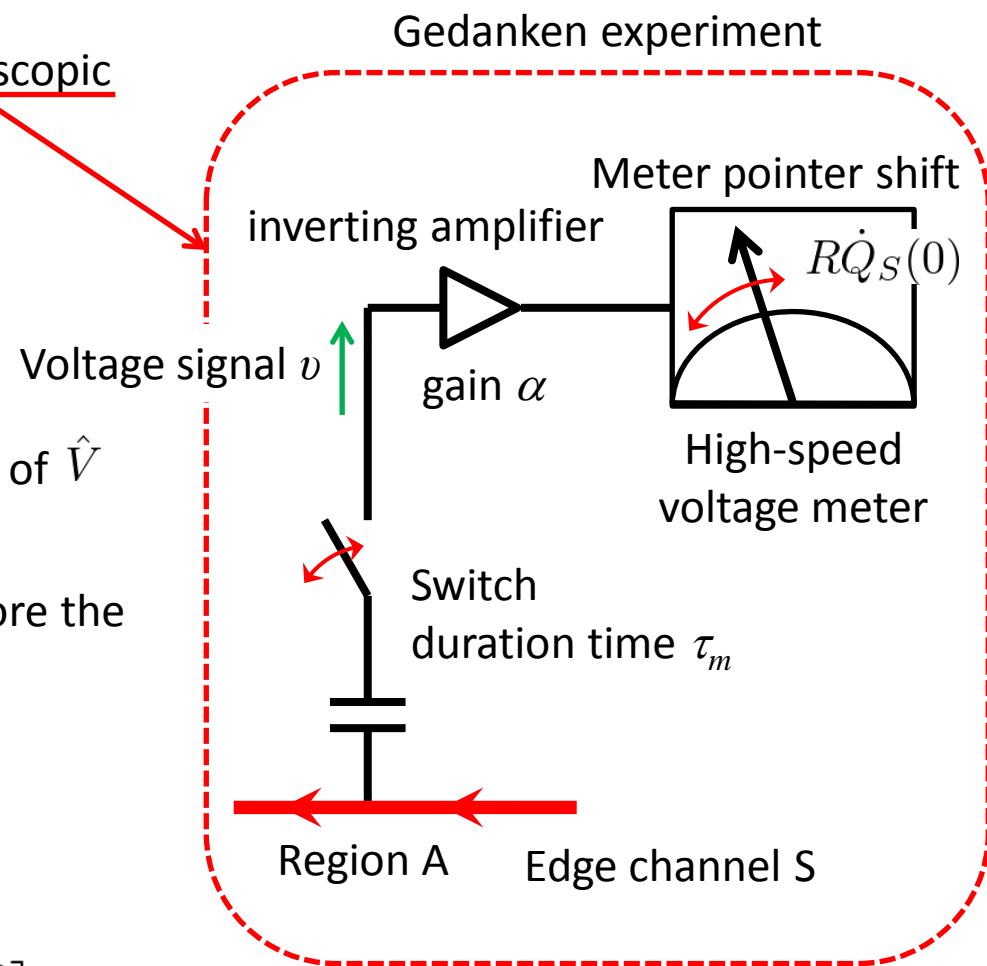
$P_{\hat{V}}$: conjugate momentum operator of \hat{V}

Wavefunction of the quantum pointer before the measurement (assumption):

$$\Psi_i(v) \propto \exp \left[-\frac{1}{4\Delta V^2} v^2 \right]$$

Wavefunction after the measurement:

$$\Psi_f(v) \propto \exp \left[-\frac{1}{4\Delta V^2} (v - R\dot{Q}_S(0))^2 \right]$$



Measurement operator

$$M_v = \left(\frac{1}{2\pi\Delta V^2} \right)^{1/4} \exp \left[-\frac{1}{4\Delta V^2} (v - R\dot{Q}_S(0))^2 \right]$$

Corresponding POVM

$$\Pi_v = M_v^\dagger M_v$$

The emergence probability density of the result being v :

$$p(v) = \langle 0_S | \Pi_v | 0_S \rangle$$

The post-measurement state of $\varrho_S(x)$ corresponding to the result being v :

$$M_v |0_S\rangle$$

The average state of $\varrho_S(x)$ right after the measurement

$$\rho_1 = \int_{-\infty}^{\infty} M_v |0_S\rangle \langle 0_S| M_v^\dagger dv$$

The energy infused by the measurement:

$$E_A = \int_{-\infty}^{\infty} \langle 0_S | M_v^\dagger H_S M_v | 0_S \rangle dv$$

$$= \frac{\hbar v_g \nu_S}{4\pi} \left(\frac{ev_g R}{2\Delta V} \right)^2 \int_{-\infty}^{\infty} dx \left(\partial_x^2 w_A(x) \right)^2 \sim 1 \text{ meV for } v_s \sim 3$$

Since the voltage meter is classical & macroscopic, the estimation of M_v and E_A remains unchanged even if the amplified signal is directly sent to region G without voltage meter.

Formulation of local operation

v -dependent unitary operation $U_v \quad |v_P\rangle = U_v|0_P\rangle$

The interaction Hamiltonian of v -dependent unitary operation U_v

$$H_v = \int_{b_- - L}^{b_+ + L} F_v(y, t) \varrho_P(y) dy \quad (4)$$

The electric potential at region G (assumption)

$$F_v(y, t) = -\frac{\pi \hbar}{\nu_P \Delta V} \lambda_B(y) \delta_{\tau_m}(t - t_o) v$$

$\delta_{\tau_m}(t - t_o)$: A real localized function $\lim_{\tau_m \rightarrow 0} \delta_{\tau_m}(t - t_o) = \delta(t - t_o)$

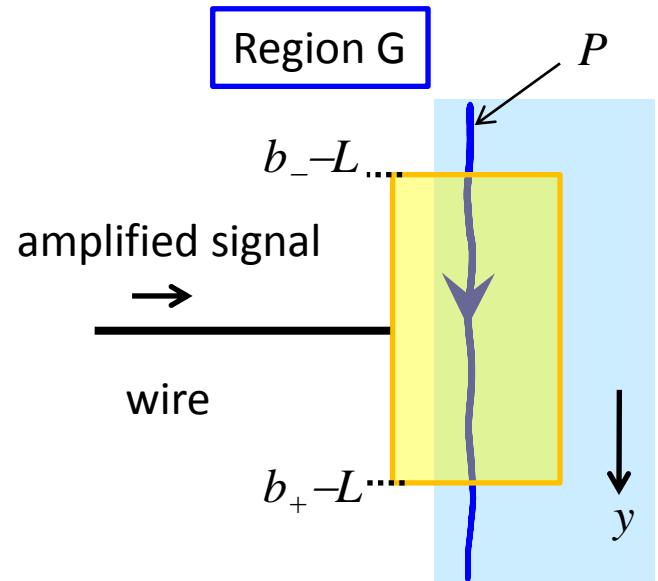
$\lambda_B(y)$: A window function related to the total number of excited electrons and quasi-holes from the vacuum state.

The gain of the amplifier:

$$\alpha = \frac{\pi \hbar}{\nu_P \Delta V \tau_m} \max_y \lambda_B(y)$$

The order of F_v

$$O(F_v) = \alpha O(v) = \alpha \Delta V$$



$\lambda_B(y)$ is related to the shape of the electrode at G.

We take the amplitude of $\lambda_B(y)$ to be the order of 10.

The unitary operation at G (displacement operator)

$$U_v = \exp \left(\frac{\pi i v}{\nu_P \Delta V} \int_{b_- - L}^{b_+ - L} \lambda_B(y) \varrho_P(y) dy \right) \quad \text{from Eq. (4)}$$

The composite state of S and P at a time T when a wave packet has been generated

$$\rho_{SP} = \int_{-\infty}^{\infty} dv e^{-\frac{iT}{\hbar} H_S} M_v |0_S\rangle\langle 0_S| M_v^\dagger e^{\frac{iT}{\hbar} H_S} \otimes |v_P\rangle\langle v_P|$$

The free Hamiltonian of the charge wave packet

$$H_B = \frac{\pi \hbar v}{\nu_P} \int_{-\infty}^{\infty} : \varrho_P(y)^2 : dy$$

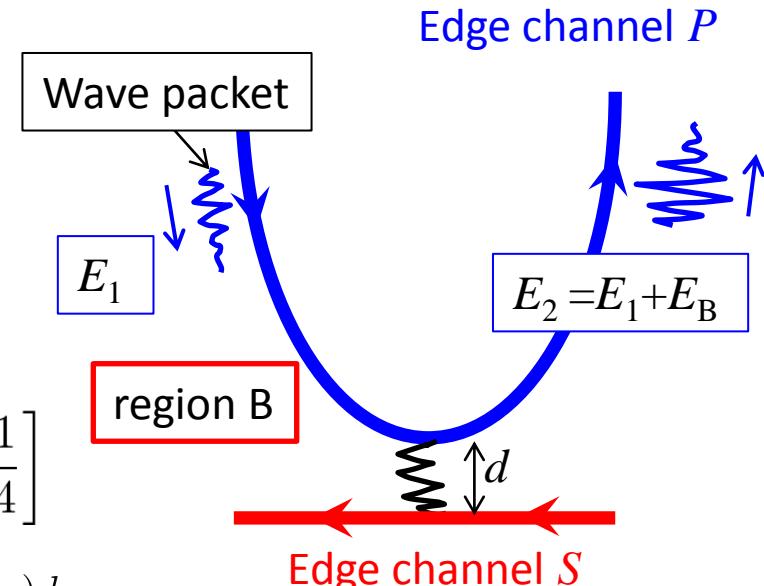
The energy average of the wave packet

$$\begin{aligned} E_1 &= \text{Tr} [H_B \rho_{SP}] \\ &= \frac{\pi \hbar v_g}{\nu_P} \int_{-\infty}^{\infty} (\partial_y \lambda_B(y))^2 dy \left[\langle 0_S | G_S^2 | 0_S \rangle + \frac{1}{4} \right] \\ G_S &= -\frac{ev_g R}{2\Delta V} \int_{-\infty}^{\infty} \varrho_S(x) \partial_x w_A(x) dx \end{aligned}$$

$$E_1 \sim 10 \text{ meV} \text{ for } \nu_S \sim 3 \text{ and } \nu_P \sim 6$$

The Coulomb interaction Hamiltonian

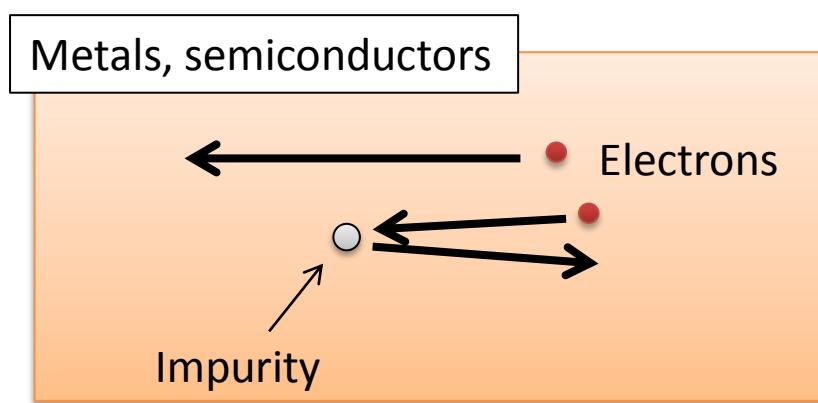
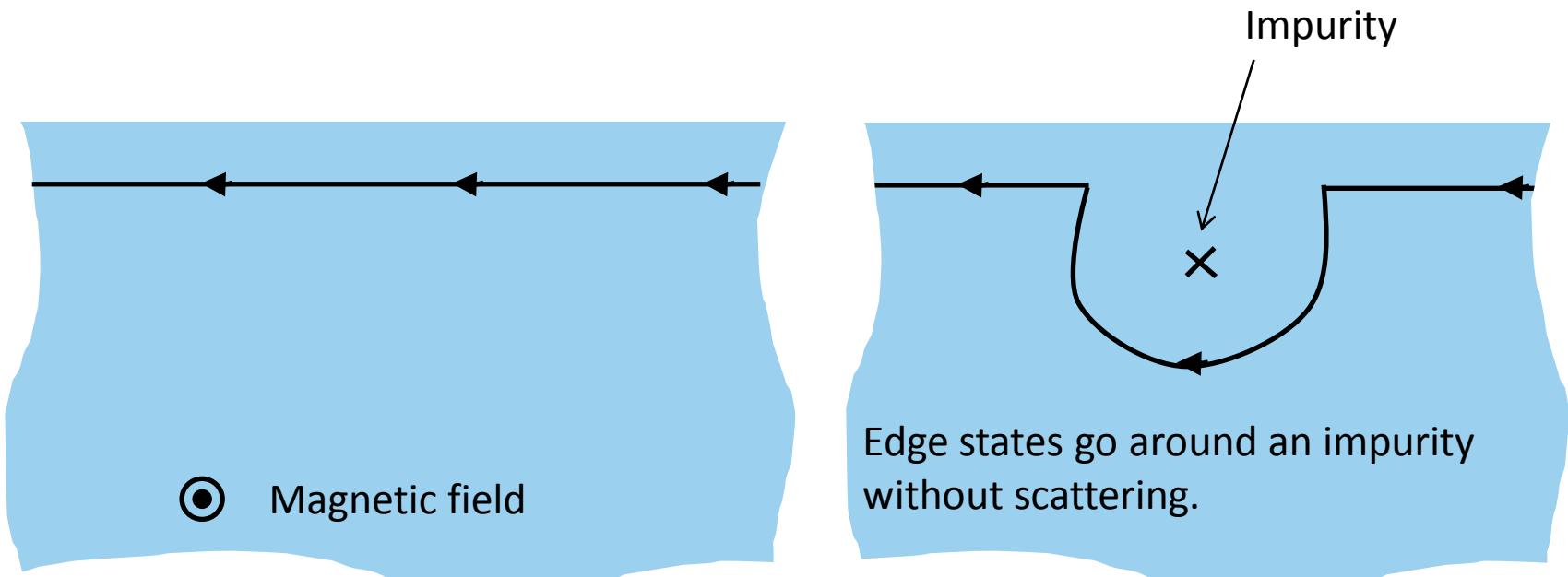
$$H_{int} = \frac{e^2}{4\pi\epsilon} \int_{b_-}^{b_+} dx \int_{b_-}^{b_+} dy \varrho_S(x) f(x, y) \varrho_P(y)$$



ϵ : Dielectric constant of GaAs

$$f(x, y) = \frac{1}{\sqrt{(x - y)^2 + d^2}}$$

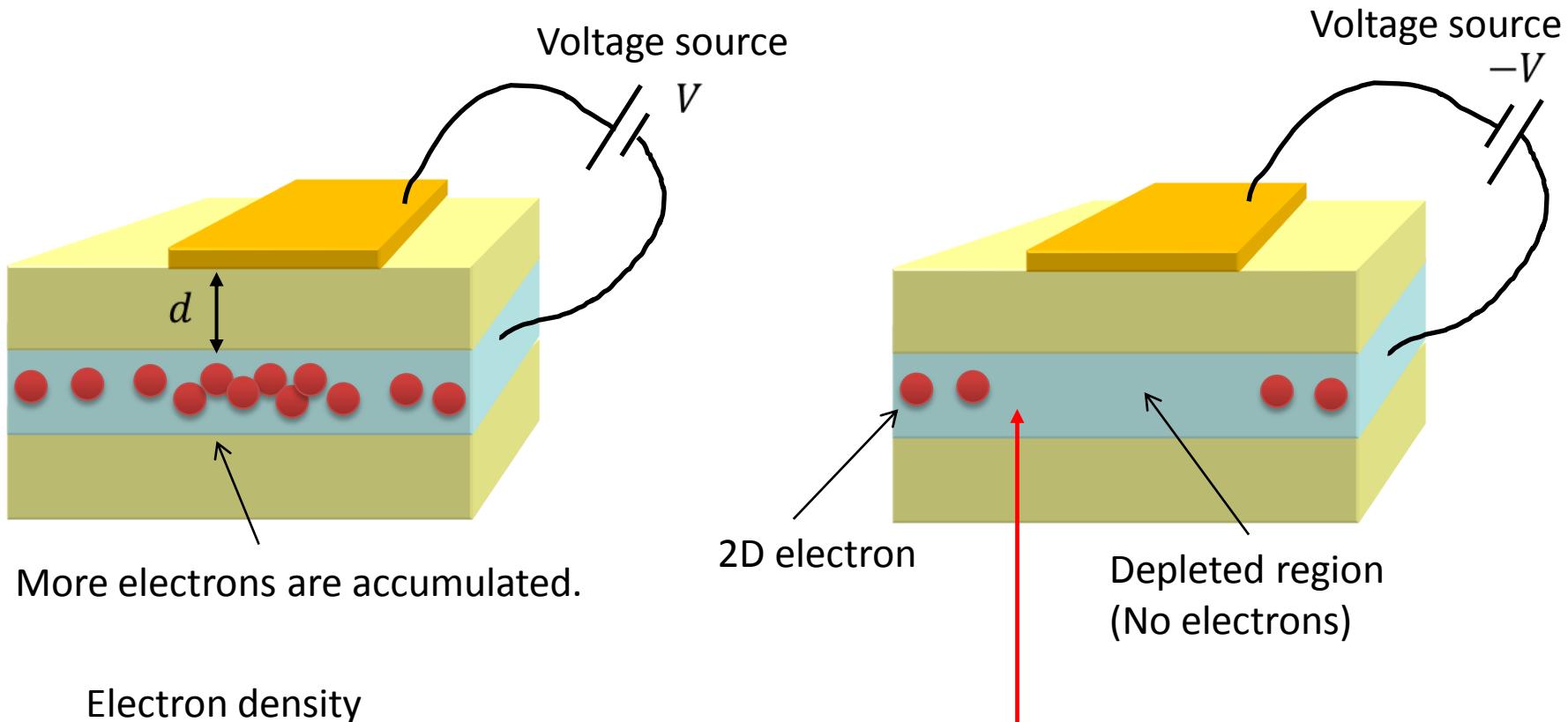
Edge state



No backscattering
=> Zero-resistance

Electrically controlled Edge channel

Electric field produced by the gate metal electrode can control electron density and the position of the edge channel.



Electron density

$$\downarrow n_e = \frac{\epsilon_r \epsilon_0}{d} V$$

The edge state are formed at this region and the position of the edge can be electrically controlled.